

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	14	((("4983544") or ("5783486") or ("6251711") or ("6316323") or ("6440851") or ("6627527") or ("66577244") or ("20030222320")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/05 13:23
S2	1916	stress and bridging and void	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:18
S3	69331	silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:18
S4	76	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:18
S5	3	("6410429").URPN.	USPAT	OR	ON	2005/09/05 10:33
S6	10	("5047367"   "5194405"   "5449642"   "5536684"   "5567652"   "5728625"   "5731239"   "5766997"   "5924010"   "5970370").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/05 10:39
S7	321	cobalt adj disilicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:28
S8	35770	titanium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:39
S9	105	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 10:39
S10	1	("6388327").URPN.	USPAT	OR	ON	2005/09/05 10:56

S11	29	("5970370").URPN.	USPAT	OR	ON	2005/09/05 11:00
S12	0	co/tin/co	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:19
S13	0	"cosi2/tin/co"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:19
S14	0	"cosi2/ti/co"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:20
S15	0	(cobalt adj disilicide near3 titanium adj nitride) adj cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:21
S16	16	cobalt adj capping adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 11:23
S17	2	cobalt adj wiring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:08
S18	3017	compressive and tensile and cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:08
S19	516928	titanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09

S20	1978	S18 and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09
S21	69331	silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09
S22	268	S20 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:09
S23	5	cobalt adj disilicide and (delamination or delaminate or delaminated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 12:29
S24	179952	compressive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23
S25	345187	tensile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23
S26	665844	laminate or laminated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23
S27	6666	S24 and S25 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:23

S28	249294	cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:24
S29	630	S27 and S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:24
S30	85312	titanium and nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:24
S31	175	S29 and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:30
S32	2820	critical adj thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:30
S33	35920	delamination	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:30
S34	78	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:33
S35	16	cobalt adj cap adj layer or cobalt adj cap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 13:33

S36	249294	cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:32
S37	116168	(densification or dimensional adj reduction or volumetric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:33
S38	7608	S36 and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:33
S39	128110	cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:33
S40	179	S38 and S39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:41
S41	1108	titanium adj nitride and capping adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:41
S42	273	S36 and S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 14:41
S43	1	("6462390").URPN.	USPAT	OR	ON	2005/09/05 15:15
S44	7	("6281102").URPN.	USPAT	OR	ON	2005/09/05 15:24
S45	264	second adj cobalt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 15:24

S46	509984	tin or titanium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 15:25
S47	53	S45 and S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/05 15:25
S48	5	("6207563").URPN.	USPAT	OR	ON	2005/09/05 15:54
S49	172871	consume or consumed or consumption	USPAT	OR	ON	2005/09/05 15:55
S50	0	sacrificial adj cobalt	USPAT	OR	ON	2005/09/05 15:55
S51	11109	S36 and S49	USPAT	OR	ON	2005/09/05 15:55
S52	684	S39 and S51	USPAT	OR	ON	2005/09/05 15:55
S53	408	S46 and S52	USPAT	OR	ON	2005/09/05 15:56
S54	301902	cap or capping	USPAT	OR	ON	2005/09/05 15:56
S55	107	S54 and S53	USPAT	OR	ON	2005/09/05 15:56
S56	0	("6743721").URPN.	USPAT	OR	ON	2005/09/05 16:00
S57	30	("4885134"   "4920073"   "5047367"   "5282946"   "5302552"   "5344793"   "5356837"   "5451545"   "5536684"   "5567651"   "5728279"   "5736461"   "5747373"   "5780362"   "5824588"   "5904564"   "5970370"   "5989988"   "6022457"   "6022795"   "6025274"   "6083817"   "6100191"   "6190516"   "6251780"   "6323130"   "6376373"   "6413859"   "6440851"   "6444578").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/05 16:00
S58	2	("6207563").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/05 16:35

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<u>NEWS 1</u>		Web Page URLs for STN Seminar Schedule - N. America
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<u>NEWS 3</u>	FEB 28	PATDPAFULL - New display fields provide for legal status data from INPADOC
<u>NEWS 4</u>	FEB 28	BABS - Current-awareness alerts (SDIs) available
<u>NEWS 5</u>	MAR 02	GBFULL: New full-text patent database on STN
<u>NEWS 6</u>	MAR 03	REGISTRY/ZREGISTRY - Sequence annotations enhanced
<u>NEWS 7</u>	MAR 03	MEDLINE file segment of TOXCENTER reloaded
<u>NEWS 8</u>	MAR 22	KOREAPAT now updated monthly; patent information enhanced
<u>NEWS 9</u>	MAR 22	Original IDE display format returns to REGISTRY/ZREGISTRY
<u>NEWS 10</u>	MAR 22	PATDPASPC - New patent database available
<u>NEWS 11</u>	MAR 22	REGISTRY/ZREGISTRY enhanced with experimental property tags
<u>NEWS 12</u>	APR 04	EPFULL enhanced with additional patent information and new fields
<u>NEWS 13</u>	APR 04	EMBASE - Database reloaded and enhanced
<u>NEWS 14</u>	APR 18	New CAS Information Use Policies available online
<u>NEWS 15</u>	APR 25	Patent searching, including current-awareness alerts (SDIs), based on application date in CA/CAPLUS and USPATFULL/USPAT2 may be affected by a change in filing date for U.S. applications.
<u>NEWS 16</u>	APR 28	Improved searching of U.S. Patent Classifications for U.S. patent records in CA/CAPLUS
<u>NEWS 17</u>	MAY 23	GBFULL enhanced with patent drawing images
<u>NEWS 18</u>	MAY 23	REGISTRY has been enhanced with source information from CHEMCATS
<u>NEWS 19</u>	JUN 06	The Analysis Edition of STN Express with Discover! (Version 8.0 for Windows) now available
<u>NEWS 20</u>	JUN 13	RUSSIAPAT: New full-text patent database on STN
<u>NEWS 21</u>	JUN 13	FRFULL enhanced with patent drawing images
<u>NEWS 22</u>	JUN 27	MARPAT displays enhanced with expanded G-group definitions and text labels
<u>NEWS 23</u>	JUL 01	MEDICONF removed from STN
<u>NEWS 24</u>	JUL 07	STN Patent Forums to be held in July 2005
<u>NEWS 25</u>	JUL 13	SCISEARCH reloaded
<u>NEWS 26</u>	JUL 20	Powerful new interactive analysis and visualization software, STN AnaVist, now available
<u>NEWS 27</u>	AUG 11	Derwent World Patents Index(R) web-based training during August
<u>NEWS 28</u>	AUG 11	STN AnaVist workshops to be held in North America
<u>NEWS 29</u>	AUG 30	CA/CAPLUS - Increased access to 19th century research documents
<u>NEWS 30</u>	AUG 30	CASREACT - Enhanced with displayable reaction conditions
<u>NEWS EXPRESS</u>	JUNE 13	CURRENT WINDOWS VERSION IS V8.0, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 13 JUNE 2005
<u>NEWS HOURS</u>		STN Operating Hours Plus Help Desk Availability
<u>NEWS INTER</u>		General Internet Information
<u>NEWS LOGIN</u>		Welcome Banner and News Items
<u>NEWS PHONE</u>		Direct Dial and Telecommunication Network Access to STN
<u>NEWS WWW</u>		CAS World Wide Web Site (general information)

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FILE 'HOME' ENTERED AT 13:08:38 ON 05 SEP 2005

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FILE LAST UPDATED: 5 SEP 2005

<20050905/UP>

FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN  
THE BASIC INDEX >>>

=> s cobalt cap layer

62465 COBALT

10598 CAP

371102 LAYER

L1 1 COBALT CAP LAYER

(COBALT (W) CAP (W) LAYER)

=> d 11

L1 ANSWER 1 OF 1 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full  
Text

AN 2001:6836533 INSPEC DN B2001-03-2560J-019

TI Base contact material issues of integrated high-speed Si/SiGe heterojunction bipolar transistors.

AU Hohaus, J.; Schreiber, H.-U. (Zentrum fuer Mikroelektronik und Syst., Bochum Univ., Germany)

SO Materialwissenschaft und Werkstofftechnik (Sept. 2000) vol.31, no.9, p.833-6. 8 refs.

Published by: Wiley-VCH Verlagsgesellschaft mbH

CODEN: MATWER ISSN: 0933-5137

SICI: 0933-5137(200009)31:9L.833:BCMI;1-1

DT Journal

TC Experimental

CY Germany, Federal Republic of

LA German

=> s cobalt capping layer

62465 COBALT

2572 CAPPING

371102 LAYER

L2 0 COBALT CAPPING LAYER

(COBALT (W) CAPPING (W) LAYER)

=> s cosi2/tin/co

'CO' IS NOT A VALID FIELD CODE

L3 0 COSI2/TIN/CO



=> s cobalt disilicide  
       62465 COBALT  
       1292 DISILICIDE  
 L4      155 COBALT DISILICIDE  
           (COBALT(W) DISILICIDE)

=> s titanium nitride  
       87724 TITANIUM  
       31667 NITRIDE  
 L5      2294 TITANIUM NITRIDE  
           (TITANIUM(W) NITRIDE)

=> s cobalt  
 L6      62465 COBALT

=> s 14 and 15 and 16  
 L7      0 L4 AND L5 AND L6

=> s 14 and 15  
 L8      0 L4 AND L5

=> s tensile  
 L9      57275 TENSILE

=> s compressive  
 L10     24399 COMPRESSIVE

=> s silicide  
 L11     8718 SILICIDE

=> s 19 and 110 and 111  
 L12     28 L9 AND L10 AND L11

=> d 112 1-28

L12 ANSWER 1 OF 28 INSPEC (C) 2005 IEE on STN



AN 2004:8335912 INSPEC DN B2005-05-2530F-008  
 TI Nanometer scale characterisation of CoSi<sub>2</sub> and NiSi induced strain in Si by convergent beam electron diffraction.  
 AU Benedetti, A.; Bender, H.; Torregiani, C. (IMEC, Leuven, Belgium); Van Dal, M.; Maex, K.  
 SO Materials Science & Engineering B (Solid-State Materials for Advanced Technology) (15 Dec. 2004) vol.B114-115, p.61-6. 11 refs.  
 Published by: Elsevier  
 Price: CCCC 0921-5107/04/\$30.00  
 CODEN: MSBTEK ISSN: 0921-5107  
 SICI: 0921-5107(20041215)B114115L:61:NSCC;1-K  
 Conference: EMRS 2004, Symposium B Material Science Issues in Advanced CMOS Source-Drain Engineering. Strasbourg, France, 2004  
 DT Conference Article; Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L12 ANSWER 2 OF 28 INSPEC (C) 2005 IEE on STN



AN 2004:8271709 INSPEC DN A2005-06-8115C-014  
 TI Preparation and properties of sputtered nitrogen-doped cobalt silicide film.  
 AU Jyh-Hua Ting (Nat. Nano Device Labs., Hsinchu, Taiwan); Shiuann-Huah Shiau; Yeong-Jyh Chen; Fu-Ming Pan; Harianto Wang; Pu, G.M.; Chung-Yuan Kung  
 SO Thin Solid Films (1 Dec. 2004) vol.468, no.1-2, p.155-60. 15 refs.  
 Published by: Elsevier  
 Price: CCCC 0040-6090/2004/\$30.00  
 CODEN: THSFAP ISSN: 0040-6090  
 SICI: 0040-6090(20041201)468:1/2L.155:PPSN;1-L  
 DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L12 ANSWER 3 OF 28 INSPEC (C) 2005 IEE on STN

Full Text  
 AN 2004:8223628 INSPEC DN A2005-03-7755-004; B2005-02-2810-011  
 TI PLD of high-k dielectric films on silicon.  
 AU Ratzke, M.; Kappa, M. (LS Experimentalphys. II, BTU Cottbus, Germany); Wolfram, D.; Kouteva-Argirova, S.; Reif, J.  
 SO Proceedings of the SPIE - The International Society for Optical Engineering (2004) vol.5662, no.1, p.406-11. 14 refs.  
 Published by: SPIE-Int. Soc. Opt. Eng  
 Price: CCCC 0277-786X/04/\$15.00  
 CODEN: PSISDG ISSN: 0277-786X  
 SICI: 0277-786X(2004)5662:1L.406:HDFS;1-M  
 Conference: Fifth International Symposium on Laser Precision Microfabrication. Nara, Japan, 11-14 May 2004  
 Sponsor(s): U.S. Air Force Office of Sci. Res., Asian Office of Aerospace Res. and Dev. (U.S. AFOSR/AOARD); Nara Convention Bur. (Japan); AIST - Nat. Inst. of Adv. Ind. Sci. and Technol. (Japan); Asahi Glass Found. for Promotion of Material Sci. and Technol. of Japan (Japan); Kao Found. for Arts and Sci. (Japan)  
 DT Conference Article; Journal  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 4 OF 28 INSPEC (C) 2005 IEE on STN

Full Text  
 AN 2003:7643197 INSPEC DN A2003-13-6822-043; B2003-07-2530D-007  
 TI Effects of stress on the interfacial reactions of metal thin films on (001)Si.  
 AU Cheng, S.L.; Lo, H.M.; Cheng, L.W.; Chang, S.M.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan)  
 SO Thin Solid Films (22 Jan. 2003) vol.424, no.1, p.33-9. 17 refs.  
 Doc. No.: S0040-6090(02)00902-1  
 Published by: Elsevier  
 Price: CCCC 0040-6090/2003/\$30.00  
 CODEN: THSFAP ISSN: 0040-6090  
 SICI: 0040-6090(20030122)424:1L.33:ESIR;1-R  
 DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L12 ANSWER 5 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 2003:7613346 INSPEC DN A2003-12-6860-029; B2003-06-2550F-011  
 TI Stress evolution in a Ti/Al(Si,Cu) dual layer during annealing.  
 AU Bostrom, O.; Gergaud, P.; Thomas, O. (Lab. TECSEN, CNRS, Marseille, France); Boivin, P.  
 SO Dislocations and Deformation Mechanisms in Thin Films and Small Structures (Material Research Society Symposium Proceedings Vol.673)  
 Editor(s): Kraft, O.; Schwarz, K.W.; Baker, S.P.; Freund, L.B.; Hull, R.  
 Warrendale, PA, USA: Mater. Res. Soc, 2001. p.P1.5.1-6 of xi+208 pp. 12 refs.  
 Conference: San Francisco, CA, USA, 17-19 April 2001  
 ISBN: 1-55899-609-5  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 6 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 2000:6596811 INSPEC DN B2000-06-2550F-094  
 TI **Silicide** contacts for sub-0.25  $\mu$ m devices.  
 AU Chen, L.J.; Cheng, S.L.; Chang, S.M.; Peng, Y.C.; Huang, H.Y.; Cheng, L.W. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan)  
 SO Advanced Interconnects and Contacts. Symposium  
 Editor(s): Edelstein, D.C.; Kikkawa, T.; Ozturk, M.C.; Tu, K.-N.; Weitzman, E.J.  
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.123-34 of xiv+977 pp. 48 refs.  
 Conference: San Francisco, CA, USA, 5-7 April 1999  
 ISBN: 1-55899-471-8  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L12 ANSWER 7 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 2000:6544519 INSPEC DN B2000-05-2530D-011  
 TI Characteristics of molybdenum nitride thin film by N<sub>2</sub><sup>+</sup> ion implantation.  
 AU Dong Joon Kim; Ik-Soo Kim; Yong Tae Kim (Semicond. Mater. Lab., Korea Inst. of Sci. & Technol., Seoul, South Korea); Jong-Wan Park  
 SO Materials Reliability in Microelectronics IX. Symposium  
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.45-50 of ix+311 pp. 6 refs.  
 Conference: San Francisco, CA, USA, 6-8 April 1999  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L12 ANSWER 8 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1999:6426396 INSPEC DN A2000-02-7340L-005; B2000-01-2530B-023  
 TI Reduction of leakage current for shallow n<sup>+</sup>/p junction fabricated using C49 TiSi<sub>2</sub> as a diffusion source.  
 AU Dong Kyun Sohn; Ji-Soo Park; Jong-Uk Bae; Byung Hak Lee; Chang Hee Han;

Jin Won Park (Div. of Res. & Dev., LG Semicon Co. Ltd., Cheongju, South Korea)

SO Journal of the Electrochemical Society (Oct. 1999) vol.146, no.10, p.3837-42. 17 refs.

Doc. No.: S0013-4651(99)01003-4

Published by: Electrochem. Soc

Price: CCCC 0013-4651/99/\$7.00

CODEN: JESOAN ISSN: 0013-4651

SICI: 0013-4651(199910)146:10L.3837:RLCS;1-7

DT Journal

TC Practical; Experimental

CY United States

LA English

L12 ANSWER 9 OF 28 INSPEC (C) 2005 IEE on STN



AN 1999:6319140 INSPEC DN A1999-18-6822-005; B1999-09-2530D-008

TI The influences of stress on the growth of Ti and Ni silicide thin films on (001)Si.

AU Chen, L.J.; Cheng, S.L.; Luo, H.M.; Huang, H.Y.; Peng, Y.C. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Tsui, B.Y.; Tsai, C.J.; Guo, S.S.

SO 1998 5th International Conference on Solid-State and Integrated Circuit Technology. Proceedings (Cat. No.98EX105)

Editor(s): Zhang, M.; Tu, K.N.

Piscataway, NJ, USA: IEEE, 1998. p.256-9 of xxi+973 pp. 6 refs.

Conference: Beijing, China, 21-23 Oct 1998

Sponsor(s): Chinese Inst. Electron.; IEEE Electron. Devices Soc.; IEEE

Solid-State Circuits Soc.; Japan Soc. Appl. Phys.; URSI Comm. D; Electron.

Div. IEEE (UK); Korea Inst. Telematics & Electron.; IEEE Beijing Sect

Price: CCCC 0 7803 4306 9/98/\$10.00

ISBN: 0-7803-4306-9

DT Conference Article

TC Experimental

CY United States

LA English

L12 ANSWER 10 OF 28 INSPEC (C) 2005 IEE on STN



AN 1999:6196577 INSPEC DN A1999-09-6822-001; B1999-05-2550F-001

TI Effects of stress on the growth of TiSi<sub>2</sub> thin films on (001)Si.

AU Cheng, S.L.; Huang, H.Y.; Peng, Y.C.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Tsui, B.Y.; Tsai, C.J.; Guo, S.S.

SO Applied Physics Letters (8 March 1999) vol.74, no.10, p.1406-8. 9 refs.

Doc. No.: S0003-6951(99)04910-4

Published by: AIP

Price: CCCC 0003-6951/99/74(10)/1406(3)/\$15.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19990308)74:10L.1406:ESGT;1-D

DT Journal

TC Experimental

CY United States



LA English

L12 ANSWER 11 OF 28 INSPEC (C) 2005 IEE on STN





AN 1999:6191894 INSPEC DN B1999-04-2550F-040  
 TI Effect of stress on **silicide** formation kinetics in thin film titanium-silicon system.  
 AU Nagabushnam, R.V.; Singh, R.K. (Dept. of Mater. Sci. & Eng., Florida Univ., Gainesville, FL, USA); Sharan, S.  
 SO Materials Science in Semiconductor Processing (1998) vol.1, no.3-4, p.249-55. 7 refs.  
 Doc. No.: S1369-8001(98)00046-8  
 Published by: Elsevier  
 Price: CCCC 1369-8001/99/\$20.00  
 CODEN: MSSPFQ ISSN: 1369-8001  
 SICI: 1369-8001(1998)1:3/4L.249:ESSF;1-M  
 Conference: E-MRS'98 Meeting. Symposium I: Rapid Thermal Processing. Strasbourg, France, 16-19 June 1998  
 DT Conference Article; Journal  
 TC Experimental  
 CY United Kingdom  
 LA English



L12 ANSWER 12 OF 28 INSPEC (C) 2005 IEE on STN

   
 AN 1999:6134944 INSPEC DN B1999-02-2550F-075  
 TI The effects of stress on the formation of titanium **silicide**.  
 AU Cheng, S.L.; Huang, H.; Peng, Y.C.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Tsui, B.Y.; Tsai, C.J.; Guo, S.S.; Yu, K.H.  
 SO Proceedings of the IEEE 1998 International Interconnect Technology Conference (Cat. No.98EX102)  
 New York, NY, USA: IEEE, 1998. p.190-2 of 304 pp. 6 refs.  
 Conference: San Francisco, CA, USA, 1-3 June 1998  
 Sponsor(s): IEEE Electron Devices Soc  
 Price: CCCC 0 7803 4285 2/98/\$10.00  
 ISBN: 0-7803-4285-2  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L12 ANSWER 13 OF 28 INSPEC (C) 2005 IEE on STN

   
 AN 1996:5256554 INSPEC DN B9606-2550F-042  
 TI Thermal stability of platinum **silicide** in deep sub-micron lines.  
 AU Dan-Xia Xu; Das, S.R.; Erickson, L. (Inst. for Microstructural Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada); Naem, A.  
 SO Materials Reliability in Microelectronics V. Symposium  
 Editor(s): Oates, A.S.; Filter, W.F.; Rosenberg, R.; Greer, A.L.; Gadepally, K.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1995. p.223-8 of xv+523 pp. 4 refs.  
 Conference: San Francisco, CA, USA, 17-21 April 1995  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 14 OF 28 INSPEC (C) 2005 IEE on STN

   
 AN 1995:5081171 INSPEC DN A9522-6822-018

TI Stress evolution during the growth of ultrathin layers of iron and iron silicide on Si(111).  
 AU Sander, D.; Enders, A.; Kirschner, J. (Max-Planck-Inst. fur Mikrostrukturphys., Halle, Germany)  
 SO Applied Physics Letters (25 Sept. 1995) vol.67, no.13, p.1833-5. 39 refs.  
 Price: CCCC 0003-6951/95/67(13)/1833/3/\$6.00  
 CODEN: APPLAB ISSN: 0003-6951  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 15 OF 28 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1995:4961282 INSPEC DN A9512-6855-041  
 TI Disordered structure of cubic iron silicide films on Si(111).  
 AU Whiteaker, K.L.; Robinson, I.K.; Benson, C. (Dept. of Phys., Illinois Univ., Urbana, IL, USA); Smilgies, D.M.; Onda, N.; von Kanel, H.  
 SO Physical Review B (Condensed Matter) (15 April 1995) vol.51, no.15, p.9715-21. 20 refs.  
 Price: CCCC 0163-1829/95/51(15)/9715(7)/\$06.00  
 CODEN: PRBMDO ISSN: 0163-1829  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 16 OF 28 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1994:4717874 INSPEC DN A9417-6855-024  
 TI Copper silicide precipitation influenced by the strain of a Ge<sub>0.02</sub>Si<sub>0.98</sub> heteroepitaxial layer.  
 AU Kissinger, G.; Morgenstern, G.; Richter, H. (Inst. fur Halbleiterphys. Frankfurt (Oder) GmbH, Germany)  
 SO Journal of Applied Physics (15 May 1994) vol.75, no.10, pt.1, p.4994-5000. 15 refs.  
 Price: CCCC 0021-8979/94/75(10)/4994/7/\$6.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 17 OF 28 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1994:4636576 INSPEC DN B9405-2560R-025  
 TI The influence of mechanical stress on hot-carrier degradation in MOSFETs.  
 AU De Wolf, I.; Bellens, R.; Groeseneken, G.; Maes, H.E. (IMEC, Leuven, Belgium)  
 SO Materials Reliability in Microelectronics III Symposium  
 Editor(s): Rodbell, K.P.; Filter, W.F.; Frost, H.J.; Ho, P.S.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1993. p.281-6 of xi+496 pp. 14 refs.  
 Conference: San Francisco, CA, USA, 12-15 April 1993  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L12 ANSWER 18 OF 28 INSPEC (C) 2005 IEE on STN

Full Text	References
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AN 1994:4620369 INSPEC DN A9408-6825-006; B9404-2530F-014  
 TI Stress measurements in silicon substrates with TiSi<sub>2</sub> patterns using Raman microprobe.  
 AU Ito, T.; Azuma, H.; Noda, S. (Toyota Central Res. & Dev. Labs. Inc., Aichi, Japan)  
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers & Short Notes) (Jan. 1994) vol.33, no.1A, p.171-7. 14 refs.  
 CODEN: JAPNDE ISSN: 0021-4922  
 DT Journal  
 TC Experimental  
 CY Japan  
 LA English

L12 ANSWER 19 OF 28 INSPEC (C) 2005 IEE on STN

Full Text	References
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AN 1993:4484539 INSPEC DN A9321-6865-003  
 TI Synthesis and properties of microlaminate structures by ion beam assisted deposition.  
 AU Was, G.S.; Jones, J.W.; Kalnas, C.E.; Parfitt, L.J.; Mashayekhi, A. (Michigan Univ., Ann Arbor, MI, USA); Hoffmann, D.W.  
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (June 1993) vol.B80-81, pt.2, p.1356-61. 18 refs.  
 Price: CCCC 0168-583X/93/\$06.00  
 CODEN: NIMBEU ISSN: 0168-583X  
 Conference: Eighth International Conference on Ion Beam Modification of Materials. Heidelberg, Germany, 7-11 Sept 1992  
 Sponsor(s): Anatech Ltd.; Bayer AG; Daimler-Benz AG; Danfysik A/S; et al  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L12 ANSWER 20 OF 28 INSPEC (C) 2005 IEE on STN

Full Text	References
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AN 1992:4161485 INSPEC DN A9213-6820-008  
 TI Silicidation reaction and stress in Ti/Si.  
 AU Chen, S.C.; Tamura, H. (VLSI R&D Center, Oki Electr. Ind. Co. Ltd., Tokyo, Japan); Hara, T.; Kinoshita, K.; Inoue, K.; Endo, N.; Nakamura, S.  
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers & Short Notes) (Feb. 1992) vol.31, no.2A, p.201-5. 14 refs.  
 CODEN: JAPNDE ISSN: 0021-4922  
 DT Journal  
 TC Experimental  
 CY Japan  
 LA English

L12 ANSWER 21 OF 28 INSPEC (C) 2005 IEE on STN

Full Text	References
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AN 1991:3990785 INSPEC DN A91135733  
 TI Influence of particle bombardment on microstructure and internal stresses of refractory metal silicides on silicon.  
 AU Hardtke, Ch.; Schilling, W.; Ullmaier, H. (Inst. fur Festkorperforschung,

Forschungszentrum Julich, Germany)

SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (July 1991) vol.B59-B60, pt.1, p.377-81. 11 refs.

Price: CCCC 0168-583X/91/\$03.50

CODEN: NIMBEU ISSN: 0168-583X

Conference: 7th International Conference on Ion Beam Modification of Materials. Knoxville, TN, USA, 9-14 Sept 1990

DT Conference Article; Journal

TC Experimental

CY Netherlands

LA English

L12 ANSWER 22 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1990:3725057 INSPEC DN A90132335

TI Interfacial reaction of Ta- and Si-rich tantalum silicides with Si substrate.

AU Hara, T.; Murota, M. (Dept. of Electr. Eng., Hosei Univ., Tokyo, Japan)

SO Journal of Applied Physics (1 July 1990) vol.68, no.1, p.183-8. 23 refs.

Price: CCCC 0021-8979/90/130183-06\$03.00

CODEN: JAPIAU ISSN: 0021-8979

DT Journal

TC Experimental

CY United States

LA English

L12 ANSWER 23 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1990:3543735 INSPEC DN A90021439

TI Stress relaxation in tantalum **silicide** films by particle bombardment.

AU Hardtke, C.; Ullmaier, H.; Schilling, W.; Gebauer, M. (Inst. fur Festkorperforschung, KFA Julich, West Germany)

SO Thin Solid Films (Aug. 1989) vol.175, p.61-5. 4 refs.

Price: CCCC 0040-6090/89/\$3.50

CODEN: THSFAP ISSN: 0040-6090

Conference: 2nd International Symposium on Trends and New Applications in Thin Films (TATF 89). Regensburg, West Germany, 27 Feb-3 March 1989

DT Conference Article; Journal

TC Experimental

CY Switzerland

LA English

L12 ANSWER 24 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3074717 INSPEC DN A88034206

TI Effect of substrate temperature on the properties of noncrystalline molybdenum **silicide** layers.

AU Bretschneider, W.; Beddies, G.; Breuer, K.; Holzhuter, G.; Leimer, V. (Tech. Univ., Karl-Marx-Stadt, East Germany)

SO Wissenschaftliche Zeitschrift der Technischen Universitaet Karl-Marx-Stadt (1987) vol.29, no.2, p.252-5. 10 refs.

ISSN: 0863-0615

DT Journal

TC Experimental

CY German Democratic Republic

LA German



L12 ANSWER 25 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1987:3014592 INSPEC DN A87142848  
 TI Stresses and radiation damage in Ar+ and Ti+ ion-implanted silicon.  
 AU Madakson, P.; Angilello, J. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)  
 SO Journal of Applied Physics (1 Sept. 1987) vol.62, no.5, p.1688-93. 14 refs.  
 Price: CCCC 0021-8979/87/171688-06\$02.40  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L12 ANSWER 26 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1983:2103377 INSPEC DN A83091259  
 TI Temperature effects on internal stress in molybdenum thin films on single-crystal silicon substrates.  
 AU Jiann-Ruey Chen; Ching-Hung Ho (Dept. of Materials Sci. & Engng., Nat. Tsing Univ., Hsinchu, Taiwan)  
 SO Thin Solid Films (17 June 1983) vol.104, no.1-2, p.251-5. 19 refs.  
 Price: CCCC 0040-6090/83/\$3.00  
 CODEN: THSFAP ISSN: 0040-6090  
 Conference: Symposium on Interfaces and Contacts. Boston, MA, USA, 1-4 Nov 1982  
 DT Conference Article; Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L12 ANSWER 27 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1975:799857 INSPEC DN A75061951  
 TI Stresses in thin nickel **silicide** films.  
 AU Koos, V.; Neumann, H.-G. (Sektion Phys. der Univ. Rostock, East Germany)  
 SO Physica Status Solidi A (16 June 1975) vol.29, no.2, p.K115-16. 3 refs.  
 CODEN: PSSABA ISSN: 0031-8965  
 DT Journal  
 TC Experimental  
 CY German Democratic Republic  
 LA English

L12 ANSWER 28 OF 28 INSPEC (C) 2005 IEE on STN

Full Text

AN 1971:256416 INSPEC DN A71033394  
 TI Effect of copper on mechanical properties, machinability, corrosion behaviour and structural stability of calcium **silicide** inoculated cast irons.  
 AU Krishna, L. (Univ. Roorkee, India); Gaindhar, J.L.  
 SO Roorkee University Research Journal (1970) vol.12, no.1-2, p.39-43  
 CODEN: RURJAX ISSN: 0557-3254  
 DT Journal  
 TC Experimental

CY India  
LA English

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L13 7557 L9 AND L10

=> s 14 and 113

L14 0 L4 AND L13

=> d 14 1-155

L4 ANSWER 1 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2005:8518110 INSPEC DN A2005-18-8140G-010  
TI Effect of annealing on CoSi<sub>2</sub> thin films prepared by magnetron sputtering.  
AU Fanxiong Cheng; Chuanhai Jiang; Jiansheng Wu (Sch. of Mater. Sci. & Eng., Shanghai Jiao Tong Univ., China)  
SO Materials Science & Engineering B (Solid-State Materials for Advanced Technology) (15 May 2005) vol.119, no.1, p.61-4. 19 refs.  
Doc. No.: S0921-5107(05)00047-4  
Published by: Elsevier  
CODEN: MSBTEK ISSN: 0921-5107  
SICI: 0921-5107(20050515)119:1L:61:EACT;1-R  
DT Journal  
TC Experimental  
CY Switzerland  
LA English

L4 ANSWER 2 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2005:8437942 INSPEC DN A2005-14-6848-004  
TI Real structure of the CoSi<sub>2</sub>/Si(001) interface studied by dedicated aberration-corrected scanning transmission electron microscopy.  
AU Falke, M.; Falke, U.; Bleloch, A. (Daresbury Lab., UK); Teichert, S.; Beddies, G.; Hinneberg, H.-J.  
SO Applied Physics Letters (16 May 2005) vol.86, no.20, p.203103-1-3. 19 refs.  
Doc. No.: S0003-6951(05)07920-9  
Published by: AIP  
Price: CCCC 0003-6951/2005/86(20)/01/01/6495(3)/\$22.50  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20050516)86:20L:203103:RSCI;1-E  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 3 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2005:8394414 INSPEC DN B2005-06-1265D-050; C2005-06-5320G-024  
TI Aggressively scaled (0.143 mu m<sup>2</sup>) 6T-SRAM cell for the 32 nm node and beyond.  
AU Fried, D.M. (Syst. & Technol. Group, IBM Semicond. R&D Center, Hopewell Junction, NY, USA); Hergenrother, J.M.; Topol, A.W.; Chang, L.; Sekaric, L.; Sleight, J.W.; McNab, S.J.; Newbury, J.; Steen, S.E.; Gibson, G.; Zhang, Y.; Fuller, N.C.M.; Bucchignano, J.; Lavoie, C.; Cabral Jr, C.;

Canaperi, D.; Dokumaci, O.; Frank, D.J.; Duch, E.A.; Babich, I.; Wong, K.; Ott, J.A.; Adams, C.D.; Dalton, T.J.; Nunes, R.; Medeiros, D.R.; Viswanathan, R.; Ketchen, M.; Jeong, M.; Haensch, W.; Guarini, K.W.

SO 2004 International Electron Devices Meeting (IEEE Cat. No.04CH37602)

Piscataway, NJ, USA: IEEE, 2005. p.261-4 of 1085 pp. 8 refs.

Conference: San Francisco, CA, USA, 13-15 Dec 2004

Price: CCCC 0 7803 8684 1/2004/\$20.00

ISBN: 0-7803-8684-1

DT Conference Article

TC Practical; Experimental

CY United States

LA English

L4 ANSWER 4 OF 155 INSPEC (C) 2005 IEE on STN



AN 2004:8314823 INSPEC DN A2005-08-8115H-028; B2005-04-0520B-010

TI Growth of epitaxial CoSi<sub>2</sub> from cobalt carbonyl on Si(100) substrate.

AU Singanamalla, R.; Greve, D.W.; Barmak, K. (Dept. of Electr. & Comput. Eng., Carnegie Mellon Univ., Pittsburgh, PA, USA)

SO Silicon Front-End Junction Formation-Physics and Technology (Materials Research Society Symposium Proceedings Vol.810)

Editor(s): Pichler, P.; Claverie, A.; Lindsay, R.; Orlowski, M.; Windl, W.

Warrendale, PA, USA: Materials Research Society, 2004. p.171-6 of xvi+494 pp. 10 refs.

Conference: San Francisco, CA, USA, 13-15 April 2004

DT Conference Article

TC Experimental

CY United States

LA English

L4 ANSWER 5 OF 155 INSPEC (C) 2005 IEE on STN



AN 2004:8198371 INSPEC DN A2005-01-6855-077; B2005-01-0520F-067

TI Structural and electrical characteristics of epitaxial CoSi<sub>2</sub> grown on n-Si<sub>0.83</sub>Ge<sub>0.17</sub>/n-Si(001) by reactive chemical vapor deposition using a Si capping layer.

AU Shin, D.O.; Ban, S.H.; Ahn, Y.S.; Lee, Y.S.; Lee, N.-E. (Dept. of Mater. Eng., Sungkyunkwan Univ., Suwon, South Korea); Shim, K.-H.

SO Thin Solid Films (30 June 2004) vol.458, no.1-2, p.269-73. 15 refs.

Published by: Elsevier

Price: CCCC 0040-6090/2004/\$30.00

CODEN: THSFAP ISSN: 0040-6090

SICI: 0040-6090(20040630)458:1/2L:269:SECE;1-L

DT Journal

TC Experimental

CY Switzerland

LA English

L4 ANSWER 6 OF 155 INSPEC (C) 2005 IEE on STN



AN 2004:8129899 INSPEC DN A2004-22-6848-001; B2004-11-2520C-006

TI Nickel disilicide/silicon(001) interface structure revealed by HAADF in an aberration corrected dedicated STEM.

AU Falke, U.; Falke, M.; Bleloch, A. (SuperSTEM, Daresbury Lab., UK)

SO Microscopy and Microanalysis (2003) vol.9, suppl.3, p.288-9. 8 refs.

Published by: Springer-Verlag

CODEN: MIMIF7 ISSN: 1431-9276

SICI: 1431-9276(2003)9+3L:288:NDSI;1-O  
 Conference: MC 2003. 31st Microscopy Conference-International Forum for  
 Advanced Microscopy. Dresden, Germany, 7-12 Sept 2003

DT Conference Article; Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 7 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 2004:7944385 INSPEC DN B2004-06-2560R-016  
 TI Experimental study of transport in nanoscale planar MOSFETs near the  
 ballistic limit.  
 AU Boeuf, F. (STMicroelectronics, Crolles, France); Jehl, X.; Sanquer, M.;  
 Skotnicki, T.  
 SO IEEE Transactions on Nanotechnology (March 2004) vol.3, no.1, p.105-9. 15  
 refs.  
 Published by: IEEE  
 Price: CCCC 1536-125X/04/\$20.00  
 CODEN: ITNECU ISSN: 1536-125X  
 SICI: 1536-125X(200403)3:1L:105:ESTN;1-C

DT Journal  
 TC Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 8 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 2004:7882082 INSPEC DN A2004-07-6170T-012; B2004-04-2550B-018  
 TI Evolution of CoSi<sub>2</sub> buried structures created by high temperature Co<sup>+</sup> ion  
 implantation into Si(100) during post-implantation annealing.  
 AU Hul'ko, O. (Dept. of Mater. Sci. & Eng., California Univ., Los Angeles,  
 CA, USA); Zinke-Allmang, M.  
 SO Surface Science (10 Dec. 2003) vol.547, no.1-2, p.219-28. 17 refs.  
 Published by: Elsevier  
 Price: CCCC 0039-6028/2003/\$30.00  
 CODEN: SUSCAS ISSN: 0039-6028  
 SICI: 0039-6028(20031210)547:1/2L:219:ECBS;1-A

DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 9 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 2004:7842954 INSPEC DN A2004-05-8115H-015  
 TI UHV/CVD growth of Co on Si(001) using cobalt carbonyl.  
 AU Zhao, Q.; Greve, D.W. (Dept. of Electr. & Comput. Eng., Carnegie Mellon  
 Univ., Pittsburgh, PA, USA); Barmark, K.  
 SO Applied Surface Science (15 Oct. 2003) vol.219, no.1-2, p.136-42. 18 refs.  
 Published by: Elsevier  
 Price: CCCC 0169-4332/03/\$30.00  
 CODEN: ASUSEE ISSN: 0169-4332  
 SICI: 0169-4332(20031015)219:1/2L:136:GUCC;1-G  
 Conference: Applied Surface Modeling: Experiment, Theory and Simulations.  
 Cleveland, OH, USA, 21-23 Aug 2002

DT Conference Article; Journal

TC Experimental  
CY Netherlands  
LA English

L4 ANSWER 10 OF 155 INSPEC (C) 2005 IEE on STN

Full Text 


AN 2003:7747512 INSPEC DN A2003-22-6865-007  
TI Bias voltage influence on the shape of cobalt-silicide nanowires.  
AU Palasantzas, G. (Dept. of Appl. Phys., Groningen Univ., Netherlands)  
SO Solid State Communications (2003) vol.127, no.3, p.219-22. 15 refs.  
Published by: Elsevier  
Price: CCCC 0038-1098/03/\$30.00  
CODEN: SSCOA4 ISSN: 0038-1098  
SICI: 0038-1098(2003)127:3L.219:BVIS;1-U  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 11 OF 155 INSPEC (C) 2005 IEE on STN

Full Text 

AN 2003:7665633 INSPEC DN A2003-15-8160C-066; B2003-08-2550E-046  
TI Cleaning after contact etching of multi-film stack and **cobalt disilicide**: an XPS study.  
AU Chooi, S.Y.M.; Lim, C.; Liu, W.-J.; Ee, P.-Y. (Adv. Module Technol. Div., Chartered Semicond. Manuf., Singapore, Singapore)  
SO Diffusion and Defect Data Part B (Solid State Phenomena) (2003) vol.92, p.243-6. 2 refs.  
Published by: Balaban Publishers; Scitec Publications  
CODEN: DDBPE8 ISSN: 1012-0394  
SICI: 1012-0394(2003)92L.243:CACE;1-B  
DT Journal  
TC Experimental  
CY Switzerland  
LA English

L4 ANSWER 12 OF 155 INSPEC (C) 2005 IEE on STN

Full Text 

AN 2003:7645274 INSPEC DN B2003-07-2550F-006  
TI Picosecond ultrasonics provides CoSi characterization.  
AU Tas, G.; Morath, C. (Rudolph Technol. Inc., USA); Stoner, R.; Lavoie, C.; Cabral, C., Jr.; Harper, J.; Yaw-Lin Huang; Huang, D.; Ren Chen  
SO Semiconductor International (Feb. 2003) vol.26, no.2, p.70-4. 10 refs.  
Published by: Cahners Publishing  
CODEN: SITLDD ISSN: 0163-3767  
SICI: 0163-3767(200302)26:2L.70:PUPC;1-K  
DT Journal  
TC Practical; Experimental  
CY United States  
LA English

L4 ANSWER 13 OF 155 INSPEC (C) 2005 IEE on STN

Full Text 

AN 2003:7636700 INSPEC DN A2003-13-6855-158; B2003-06-2550B-094  
TI A self-aligned silicide process utilizing ion implants for reduced silicon consumption and control of the silicide formation temperature.

AU Cohen, G.M.; Cabral, C., Jr.; Lavoie, C.; Solomon, P.M.; Guarini, K.W.; Chan, K.K.; Roy, R.A. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)

SO Silicon Materials - Processing, Characterization and Reliability Symposium (Mater. Res. Soc. Proceedings Vol. 716)  
Editor(s): Veteran, J.L.; O'Meara, D.L.; Misra, V.; Ho, P.S.  
Warrendale, PA, USA: Mater. Res. Soc, 2002. p.35-40 of xvii+672 pp. 6 refs.  
Conference: San Francisco, CA, USA, 1-5 April 2002  
ISBN: 1-55899-652-4

DT Conference Article  
TC Experimental  
CY United States  
LA English

L4 ANSWER 14 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7456994 INSPEC DN A2003-01-8120V-014; B2003-01-0587-012  
TI The oriented growth of carbon nanotubes on Si(100).  
AU Rotkina, L.; Shah, S.; Choi, H.; Lyding, J.W. (Beckman Inst. for Adv. Sci. & Technol., Illinois Univ., Urbana, IL, USA)  
SO AIP Conference Proceedings (2001) no.591, p.247-50. 6 refs.  
Published by: AIP  
Price: CCCC 0094-243X/01/\$18.00  
CODEN: APCPCS ISSN: 0094-243X  
SICI: 0094-243X(2001)591L:247:OGCN;1-U  
Conference: Electronic Properties of Molecular Nanostructures: 15th International Winterschool/Euroconference. Kirchberg, Austria, 3-10 March 2001

DT Conference Article; Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 15 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7435224 INSPEC DN A2002-24-6855-014  
TI Initial stages of **cobalt disilicide** formation on silicon single crystals.  
AU Gomoyunova, M.V.; Pronin, I.I.; Valdaitsev, D.A.; Faradzhev, N.S. (A.F. Ioffe Phys. Tech. Inst., St. Petersburg, Russia); Luches, P.; Rota, A.; Valeri, S.  
SO Physics of Low-Dimensional Structures (2002) no.3-4, p.163-76. 31 refs.  
Published by: VSV Co. Ltd  
CODEN: PLDSFC ISSN: 0204-3467  
SICI: 0204-3467(2002)3/4L:163:ISCD;1-1

DT Journal  
TC Experimental  
CY Russian Federation  
LA English

L4 ANSWER 16 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7418663 INSPEC DN A2002-23-6170T-006; B2002-11-2550B-027  
TI Influence of ion implantation induced defects on formation of buried CoSi<sub>2</sub> structures in Si(100).  
AU Hul'ko, O. (Dept. of Phys. & Astron., Univ. of Western Ontario, London, Ont., Canada); Fraser, J.; Zinke-Allmann, M.

SO Thin Solid Films (24 June 2002) vol.413, no.1-2, p.52-8. 17 refs.  
 Doc. No.: S0040-6090(02)00279-1  
 Published by: Elsevier  
 Price: CCCC 0040-6090/02/\$22.00  
 CODEN: THSFAP ISSN: 0040-6090  
 SICI: 0040-6090(20020624)413:1/2L:52:IIID;1-L

DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L4 ANSWER 17 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Reference**

AN 2002:7363235 INSPEC DN A2002-20-6855-030; B2002-10-0520-002  
 TI Reactive epitaxy of **cobalt disilicide** on Si(100).  
 AU Gomoyunova, M.V.; Pronin, I.I.; Valdaitsev, D.A.; Faradzhev, N.S. (A.F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia)  
 SO Physics of The Solid State (June 2002) vol.44, no.6, p.1176-80. 29 refs.  
 Published by: MAIK Nauka  
 Price: CCCC 1063-7834/02/4406-1176\$22.00  
 CODEN: PSOSD ISSN: 1063-7834  
 SICI (Trl): 1063-7834(200206)44:6L:1176:RECD;1-1  
 Translation of: Fizika Tverdogo Tela (June 2002) vol.44, no.6, p.1126-30. 29 refs.  
 CODEN: FTVTAC ISSN: 0367-3294  
 SICI: 0367-3294(200206)44:6L:1126;1-V  
 DT Journal; Translation Abstracted  
 TC Experimental  
 CY Russian Federation; Russian Federation  
 LA English

L4 ANSWER 18 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Reference**

AN 2002:7361117 INSPEC DN A2002-19-7360D-002; B2002-10-2520M-006  
 TI A study on the polycrystalline silicon germanium gate electrode fabrication technology for cobalt silicide process.  
 AU Sato, H.; Sukegawa, T.; Mori, T.; Suzuki, K.; Mori, H. (Manuf. Technol. Dev. Div., Fujitsu Ltd., Mie, Japan)  
 SO Gate Stack and Silicide Issues in Silicon Processing II. Symposium (Materials Research Society Symposium Proceedings Vol.670)  
 Editor(s): Campbell, S.A.; Clevengr, L.A.; Griffin, P.B.; Hobbs, C.C.  
 Warrendale, PA, USA: Mater. Res. Soc, 2002. p.K5.10.1-6 of xi+262 pp. 4 refs.  
 Conference: San Francisco, CA, USA, 17-19 April 2001  
 ISBN: 1-55899-606-0  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 19 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Reference**

AN 2002:7297866 INSPEC DN A2002-15-6855-022  
 TI Atomic level characterization of ultrathin flat **cobalt disilicide** film with three crystalline domains.  
 AU Ohtomo, T.; Kawasaki, T.; Takai, Y. (Dept. of Material & Life Sci., Osaka Univ., Japan)

SO Journal of Applied Physics (15 June 2002) vol.91, no.12, p.9663-6. 18 refs.

Doc. No.: S0021-8979(02)10812-7

Published by: AIP

Price: CCCC 0021-8979/2002/91(12)/9663(4)/\$19.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(20020615)91:12L:9663:ALCU;1-P

DT Journal

TC Experimental

CY United States

LA English

L4 ANSWER 20 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2002:7136176 INSPEC DN A2002-03-7125P-006

TI Electron momentum density distribution in **cobalt disilicide**: Analysis by the maximum entropy method.

AU Bellin, Ch.; Dobrzynski, L.; Kouba, H.; Loupiau, G. (LMCP, Paris VI Univ., France); Buslaps, T.; Honkimaki, V.

SO Zeitschrift fur Physikalische Chemie (2001) vol.215, no.11, p.1367-87. 28 refs.

Published by: Oldenbourg

Price: CCCC 0942-9352/01/\$3.00

CODEN: ZPCFAX ISSN: 0942-9352

SICI: 0942-9352(2001)215:11L:1367:EMDD;1-V

DT Journal

TC Theoretical

CY Germany, Federal Republic of

LA English

L4 ANSWER 21 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2001:6959674 INSPEC DN A2001-15-6630N-001

TI Formation of Co-Si intermetallics in bulk diffusion couples. I. growth kinetics and mobilities of species in the silicide phases.

AU Van Dal, M.J.H.; Huibers, D.G.G.M.; Kodentsov, A.A.; Van Loo, F.J.J. (Lab. for Solid State Chem. & Mater. Sci., Eindhoven Univ. of Technol., Netherlands)

SO Intermetallics (2001) vol.9, no.5, p.409-21. 42 refs.

Doc. No.: S0966-9795(01)00018-8

Published by: Elsevier

Price: CCCC 0966-9795/2001/\$20.00

CODEN: IERME5 ISSN: 0966-9795

SICI: 0966-9795(2001)9:5L:409:FIBD;1-V

DT Journal

TC Experimental

CY United Kingdom

LA English

L4 ANSWER 22 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2001:6945449 INSPEC DN A2001-14-6822-002

TI XAFS studies of the formation of cobalt silicide on ( square root 3\* square root 3) SiC(0001).

AU Platow, W.; Wood, D.E.; Burnette, J.E.; Nemanich, R.J.; Sayers, D.E. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)

SO Journal of Synchrotron Radiation (1 March 2001) vol.8, pt.2, p.475-7. 5



refs.

Published by: Munksgaard International Booksellers and Publishers for Int.  
Union Crystallogr

CODEN: JSYRES ISSN: 0909-0495

SICI: 0909-0495(20010301)8:2L.475:XSFC;1-V

Conference: Eleventh International Conference on X-Ray Absorption Fine  
Structure. XAFS XI. Ako, Japan, 26-31 July 2000

DT Conference Article; Journal

TC Experimental

CY Denmark

LA English

L4 ANSWER 23 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

Full  
Text

AN 2001:6935589 INSPEC DN A2001-13-7960-005

TI Theoretical photoemission and X-ray emission spectra of nickel and  
**cobalt disilicide** films.

AU Pereslavl'tseva, N.S.; Kurganskii, S.I. (Voronezh State Univ., Russia)

SO Journal of Electron Spectroscopy and Related Phenomena (March 2001)  
vol.114-116, p.549-54. 19 refs.

Doc. No.: S0368-2048(00)00345-5

Published by: Elsevier

Price: CCCC 0368-2048/2001/\$20.00

CODEN: JESRAW ISSN: 0368-2048

SICI: 0368-2048(200103)114/116L.549:TPES;1-9

Conference: Eighth International Conference on Electronic Spectroscopy and  
Structure. Berkeley, CA, USA, 8-12 Aug 2000

DT Conference Article; Journal

TC Theoretical

CY Netherlands

LA English

L4 ANSWER 24 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

Full  
Text

AN 2001:6928258 INSPEC DN A2001-12-6855-065

TI Formation of **cobalt disilicide** films on ( square root 3\* square root  
3)6H-SiC(0001).

AU Platow, W.; Wood, D.K.; Tracy, K.M.; Burnette, J.E.; Nemanich, R.J.;  
Sayers, D.E. (Dept. of Phys., North Carolina State Univ., Raleigh, NC,  
USA)

SO Physical Review B (Condensed Matter and Materials Physics) (15 March 2001)  
vol.63, no.11, p.115312/1-7. 25 refs.

Doc. No.: S0163-1829(01)04307-7

Published by: APS through AIP

Price: CCCC 0163-1829/2001/63(11)/115312(7)/\$15.00

CODEN: PRBMDO ISSN: 0163-1829

SICI: 0163-1829(20010315)63:11L.1:FCDF;1-L

DT Journal

TC Experimental

CY United States

LA English

L4 ANSWER 25 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

Full  
Text

AN 2001:6903035 INSPEC DN A2001-10-6855-098; B2001-05-0520D-031

TI Reactive epitaxy of **cobalt disilicide** on Si(111).

AU Gomoyunova, M.V.; Pronin, I.I.; Valdaitsev, D.A.; Faradzhev, N.S. (A.F.

Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia)  
 SO Physics of The Solid State (March 2001) vol.43, no.3, p.569-73. 36 refs.  
 Published by: MAIK Nauka  
 Price: CCCC 1063-7834/2001/4303-0569\$21.00  
 CODEN: PSOSD ISSN: 1063-7834  
 SICI (Tr1): 1063-7834(200103)43:3L.569:RECD;1-3  
 Translation of: Fizika Tverdogo Tela (March 2001) vol.43, no.3, p.549-53.  
 36 refs.  
 CODEN: FTVTAC ISSN: 0367-3294  
 SICI: 0367-3294(200103)43:3L.549;1-R  
 DT Journal; Translation Abstracted  
 TC Experimental  
 CY Russian Federation; Russian Federation  
 LA English

L4 ANSWER 26 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	INSPEC
AN 2001:6893009	INSPEC DN A2001-10-6822-016; B2001-05-2550A-005
TI Role of ripening and defects in the formation of mesotaxial <b>cobalt-disilicide</b> layers.	
AU Hul'ko, O. (Dept. of Phys. & Astron., Univ. of Western Ontario, London, Ont., Canada); McCaffrey, J.P.; Zinke-Allmang, M.	
SO Ultramicroscopy (Jan. 2001) vol.86, no.1-2, p.39-48. 27 refs.	
Doc. No.: S0304-3991(00)00090-5	
Published by: Elsevier	
Price: CCCC 0304-3991/2001/\$20.00	
CODEN: ULTRD6 ISSN: 0304-3991	
SICI: 0304-3991(200101)86:1/2L.39:RRDF;1-9	
Conference: SPM 2000. Second International Conference on Scanning Probe Microscopy, Sensors and Nanostructures. Heidelberg, Germany, 28-31 May 2000	
DT Conference Article; Journal	
TC Experimental	
CY Netherlands	
LA English	

L4 ANSWER 27 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	INSPEC
AN 2000:6754286	INSPEC DN B2000-12-2550F-115
TI Thermal stability improvement of <b>cobalt disilicide</b> thin films on (001)Si by high temperature sputtering deposition.	
AU Huang, H.Y.; Chen, L.J. (Dept. of Mater. Sci. & Eng., Nat. Tsing Hua Univ., Hsinchu, Taiwan); Wu, W.F.; Yang, R.P.	
SO Advances in Rapid Thermal Processing. Proceedings of the Symposium. (Electrochemical Society Proceeding Vol.99-10)	
Editor(s): Roozeboom, F.; Gelpey, J.C.; Ozturk, M.; Nakos, J.	
Pennington, NJ, USA: Electrochem. Soc, 1999. p.257-61 of xii+452 pp. 9 refs.	
Conference: Seattle, WA, USA, 3-6 May 1999	
Sponsor(s): Electrochem. Soc	
ISBN: 1-56677-232-X	
DT Conference Article	
TC Practical; Experimental	
CY United States	
LA English	

L4 ANSWER 28 OF 155 INSPEC (C) 2005 IEE on STN



AN 2000:6718461 INSPEC DN A2000-21-7125T-004  
 TI Electronic structure of **cobalt disilicide** film.  
 AU Kurganskii, S.I.; Pereslavl'tseva, N.S. (Voronezh State Univ., Russia)  
 SO Physics of The Solid State (Aug. 2000) vol.42, no.8, p.1542-7. 12 refs.  
 Published by: MAIK Nauka  
 Price: CCCC 1063-7834/2000/4208-1542\$20.00  
 CODEN: PSOSD ISSN: 1063-7834  
 SICI (Trl): 1063-7834(200008)42:8L.1542:ESCD;1-T  
 Translation of: Fizika Tverdogo Tela (Aug. 2000) vol.42, no.8, p.1499-504.  
 12 refs.  
 CODEN: FTVTAC ISSN: 0367-3294  
 SICI: 0367-3294(200008)42:8L.1499;1-4  
 DT Journal; Translation Abstracted  
 TC Theoretical  
 CY Russian Federation; Russian Federation  
 LA English

L4 ANSWER 29 OF 155 INSPEC (C) 2005 IEE on STN



AN 2000:6672711 INSPEC DN B2000-09-2550F-030  
 TI Study of capping layers, cleaning method, and rapid thermal processing  
 temperature on cobalt silicide formation.  
 AU Saigal, D.; Lai, G.; Yang, L.; Su, J.; Ngan, K.; Narasimhan, M.; Chen, F.;  
 Singhal, A.; Lopes, D. (Appl. Mater. Inc., Santa Clara, CA, USA); Lian,  
 S.; Cao, W.; Tsai, K.; Lo, P.; Lee, S.K.; Shih, J.  
 SO Proceedings of the SPIE - The International Society for Optical  
 Engineering (1999) vol.3883, p.84-95. 8 refs.  
 Published by: SPIE-Int. Soc. Opt. Eng  
 Price: CCCC 0277-786X/99/\$10.00  
 CODEN: PSISDG ISSN: 0277-786X  
 SICI: 0277-786X(1999)3883L.84:SCLC;1-R  
 Conference: Multilevel Interconnect Technology III. Santa Clara, CA, USA,  
 22-23 Sept 1999  
 Sponsor(s): SPIE  
 DT Conference Article; Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 30 OF 155 INSPEC (C) 2005 IEE on STN



AN 2000:6596816 INSPEC DN B2000-06-2550F-099  
 TI Formation and characterization of SPE grown ultra-thin **cobalt  
 disilicide** film.  
 AU Xin-Ping Qu (Dept. of Electron. Eng., Fudan Univ., Shanghai, China);  
 Guo-Ping Ru; Bing-Zong Li; Detavernier, C.; Van Meirhaeghe, R.L.; Cardon,  
 F.  
 SO Advanced Interconnects and Contacts. Symposium  
 Editor(s): Edelstein, D.C.; Kikkawa, T.; Ozturk, M.C.; Tu, K.-N.;  
 Weitzman, E.J.  
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.157-62 of xiv+977 pp. 12  
 refs.  
 Conference: San Francisco, CA, USA, 5-7 April 1999  
 ISBN: 1-55899-471-8  
 DT Conference Article  
 TC Practical; Experimental

CY United States  
LA English

L4 ANSWER 31 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2000:6496152 INSPEC DN A2000-06-6180J-004; B2000-03-2550B-019  
TI Radiation damage in focused ion beam implantation.  
AU Hausmann, S.; Bischoff, L.; Teichert, J.; Voelskow, M.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf eV, Germany)  
SO Digest of Papers. Microprocesses and Nanotechnology '99. 1999 International Microprocesses and Nanotechnology Conference Tokyo, Japan: Japan Society of Applied Physics, 1999. p.146-7 of xxii+234 pp. 4 refs.  
Conference: Yokohama, Japan, 6-8 July 1999  
Sponsor(s): Japan Soc. of Appl. Phys.; IEEE Electron Device Soc  
ISBN: 4-930813-97-2  
DT Conference Article  
TC Experimental  
CY Japan  
LA English

L4 ANSWER 32 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2000:6492138 INSPEC DN A2000-06-6822-004; B2000-03-2550F-030  
TI Effect of lateral dimensional scaling on the thermal stability of poly-CoSi<sub>2</sub> reacted on Si(001).  
AU Alberti, A. (INFM, Catania, Italy); La Via, F.; Ravesi, S.; Rimini, E.  
SO Microelectronic Engineering (Jan. 2000) vol.50, no.1-4, p.179-86. 15 refs.  
Doc. No.: S0167-9317(99)00280-4  
Published by: Elsevier  
Price: CCCC 0167-9317/2000/\$20.00  
CODEN: MIENEF ISSN: 0167-9317  
SICI: 0167-9317(200001)50:1/4L.179:ELDS;1-Q  
Conference: Third European Workshop on Materials for Advanced Metallization. Ostende, Belgium, 7-10 March 1999  
DT Conference Article; Journal  
TC Experimental  
CY Netherlands  
LA English

L4 ANSWER 33 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2000:6472583 INSPEC DN A2000-04-6170T-007; B2000-02-2550B-038  
TI Dwell-time related effects in focused ion beam synthesis of **cobalt disilicide**.  
AU Hausmann, S.; Bischoff, L.; Teichert, J.; Voelskow, M.; Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf, Dresden, Germany)  
SO Journal of Applied Physics (1 Jan. 2000) vol.87, no.1, p.57-62. 21 refs.  
Doc. No.: S0021-8979(90)03901-9  
Published by: AIP  
Price: CCCC 0021-8979/2000/87(1)/57(6)/\$15.00  
CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(20000101)87:1L.57:DTRE;1-O  
DT Journal  
TC Experimental

CY United States  
LA English

L4 ANSWER 34 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 2000:6464472 INSPEC DN A2000-04-6475-001  
TI Germanium segregation in the Co/SiGe/Si(001) thin film system.  
AU Goeller, P.T.; Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA); Myers, A.F.; Steel, E.B.  
SO Journal of Materials Research (Nov. 1999) vol.14, no.11, p.4372-84. 57 refs.  
Published by: Mater. Res. Soc  
Price: CCCC 0884-2914/99/\$2.50  
CODEN: JMREEE ISSN: 0884-2914  
SICI: 0884-2914(199911)14:11L.4372:GSST;1-6  
DT Journal  
TC Bibliography; Experimental  
CY United States  
LA English

L4 ANSWER 35 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1999:6406812 INSPEC DN A1999-24-6170W-003; B1999-12-2530D-034  
TI Solid solubility of As in CoSi<sub>2</sub> and redistribution at the CoSi<sub>2</sub>/Si interface.  
AU Mangelinck, D. (Inst. of Mater. Res. & Eng., Kent Ridge, Singapore); Cardenas, J.; d'Heurle, F.M.; Svensson, B.G.; Gas, P.  
SO Journal of Applied Physics (1 Nov. 1999) vol.86, no.9, p.4908-15. 38 refs.  
Doc. No.: S0021-8979(99)08121-9  
Published by: AIP  
Price: CCCC 0021-8979/99/86(9)/4908(8)/\$15.00  
CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(19991101)86:9L.4908:SSCR;1-S  
DT Journal  
TC Theoretical; Experimental  
CY United States  
LA English

L4 ANSWER 36 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1999:6406755 INSPEC DN A1999-24-7340N-013; B1999-12-2530D-032  
TI Abnormal junction leakage characteristics in titanium-capped **cobalt disilicide**.  
AU Chang-Yong Kang; Dae-Gwan Kang; Joo-Wan Lee (R&D Div., LG Semicon Co. Ltd., Cheongju, South Korea)  
SO Journal of Applied Physics (1 Nov. 1999) vol.86, no.9, p.5293-5. 10 refs.  
Doc. No.: S0021-8979(99)04821-5  
Published by: AIP  
Price: CCCC 0021-8979/99/86(9)/5293(3)/\$15.00  
CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(19991101)86:9L.5293:AJLC;1-V  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 37 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text Available

AN 1999:6360440 INSPEC DN A1999-21-6822-001  
 TI The effect of germanium on the Co-SiGe thin-film reaction.  
 AU Boyanov, B.I.; Goeller, P.T.; Sayers, D.E.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)  
 SO Journal of Synchrotron Radiation (1 May 1999) vol.6, no.3, p.521-3. 8 refs.  
 Published by: Munksgaard International Booksellers and Publishers for Int. Union Crystallogr  
 CODEN: JSYRES ISSN: 0909-0495  
 SICI: 0909-0495(19990501)6:3L:521:EGST;1-G  
 Conference: Tenth International Conference on X-Ray Absorption Fine Structure. XAFS X. Chicago, IL, USA, 10-14 Aug 1998  
 DT Conference Article; Journal  
 TC Experimental  
 CY Denmark  
 LA English

L4 ANSWER 38 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1999:6355468 INSPEC DN A1999-20-6822-023; B1999-10-2550F-042  
 TI Thermal stability of cobalt silicide stripes on Si (001).  
 AU Alberti, A. (Dipt. di Fisica, Catania Univ., Italy); La Via, F.; Raineri, V.; Rimini, E.  
 SO Journal of Applied Physics (15 Sept. 1999) vol.86, no.6, p.3089-95. 20 refs.  
 Doc. No.: S0021-8979(99)04918-X  
 Published by: AIP  
 Price: CCCC 0021-8979/99/86(6)/3089(7)/\$15.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 SICI: 0021-8979(19990915)86:6L:3089:TSCS;1-1  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 39 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1999:6326626 INSPEC DN A1999-19-6822-005  
 TI Reaction and thermal stability of **cobalt disilicide** on polysilicon resulting from a Si/Ti/Co multilayer system.  
 AU Alberti, A. (Dipt. di Fisica, Catania Univ., Italy); La Via, F.; Rimini, F.  
 SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (July 1999) vol.17, no.4, p.1448-55. 20 refs.  
 Doc. No.: S0734-211X(99)01404-3  
 Published by: AIP for American Vacuum Soc  
 Price: CCCC 0734-211X/99/17(4)/1448(8)/\$15.00  
 CODEN: JVTBD9 ISSN: 0734-211X  
 SICI: 0734-211X(199907)17:4L:1448:RTSC;1-G  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 40 OF 155 INSPEC (C) 2005 IEE on STN



AN 1999:6309004 INSPEC DN A1999-17-6170T-018; B1999-09-2550B-018  
 TI Initial stages of **cobalt-disilicide** formation in mesotaxy.  
 AU Carlow, G.R.; Zinke-Allmang, M. (Dept. of Phys. & Astron., Univ. of Western Ontario, London, Ont., Canada)  
 SO Canadian Journal of Chemistry (Nov. 1998) vol.76, no.11, p.1737-45. 29 refs.  
 Published by: Natl. Res. Council Canada  
 Price: CCCC 0008-4042/98/\$7.00  
 CODEN: CJCHAG ISSN: 0008-4042  
 SICI: 0008-4042(199811)76:11L:1737:ISCD;1-6  
 DT Journal  
 TC Experimental  
 CY Canada  
 LA English

L4 ANSWER 41 OF 155 INSPEC (C) 2005 IEE on STN



AN 1999:6226422 INSPEC DN B1999-05-2550N-020  
 TI Nanopatterning of thin **cobalt disilicide** layers by local oxidation.  
 AU Klinkhammer, F.; Kappius, L.; Antons, A.; Dolle, M.; Trinkaus, H.; Mesters, S.; Bochem, H.-P.; Mantl, S. (Forschungszentrum Julich GmbH, Germany); Heinig, K.-H.  
 SO Advanced Interconnects and Contact Materials and Processes for Future Integrated Circuits. Symposium  
 Editor(s): Murarka, S.P.; Eizenberg, M.; Fraser, D.B.; Madar, R.; Tung, R. Warrendale, PA, USA: Mater. Res. Soc, 1998. p.163 of xvi+560 pp. 0 refs.  
 Conference: San Francisco, CA, USA, 13-16 April 1998  
 ISBN: 1-55899-420-3  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 42 OF 155 INSPEC (C) 2005 IEE on STN



AN 1999:6220409 INSPEC DN B1999-05-2550F-087  
 TI Growth, patterning and microelectronic applications of epitaxial **cobalt disilicide**.  
 AU Mantl, S.; Kappius, L.; Antons, A.; Loken, M.; Klinkhammer, F.; Dolle, M.; Zhao, Q.T.; Mesters, S.; Buchal, C.; Bay, H.L. (Inst. fur Schicht- und Ionentechnik, Forschungszentrum Julich GmbH, Germany); Kabius, B.; Trinkaus, H.; Heinig, K.H.  
 SO Advanced Interconnects and Contact Materials and Processes for Future Integrated Circuits. Symposium  
 Editor(s): Murarka, S.P.; Eizenberg, M.; Fraser, D.B.; Madar, R.; Tung, R. Warrendale, PA, USA: Mater. Res. Soc, 1998. p.145-55 of xvi+560 pp. 24 refs.  
 Conference: San Francisco, CA, USA, 13-16 April 1998  
 ISBN: 1-55899-420-3  
 DT Conference Article  
 TC Application; Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 43 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN



AN 1999:6211931 INSPEC DN A1999-10-6180J-042; B1999-05-2550B-112  
 TI Dwell-time effects in focused ion beam synthesis of **cobalt disilicide**:  
 reflectivity measurements.  
 AU Hausmann, S.; Bischoff, L.; Voelskow, M.; Teichert, J.; Moller, W. (Inst.  
 fur Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf  
 e.V., Dresden, Germany); Fuhrmann, H.  
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam  
 Interactions with Materials and Atoms) (Jan. 1999) vol.148, no.1-4,  
 p.610-14. 12 refs.  
 Doc. No.: S0168-583X(98)00786-1  
 Published by: Elsevier  
 Price: CCCC 0168-583X/98/\$19.00  
 CODEN: NIMBEU ISSN: 0168-583X  
 SICI: 0168-583X(199901)148:1/4L.610:DTEF;1-O  
 Conference: Eleventh International Conference on Ion Beam Modification of  
 Materials. Amsterdam, Netherlands, 31 Aug-4 Sept 1998  
 Sponsor(s): Found. Fundamental Res. Matter; Utrecht Univ.; Philips Res.;  
 KLM Royal Dutch Airlines; et al  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 44 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN



AN 1999:6211799 INSPEC DN A1999-10-6170T-020; B1999-05-2550B-046  
 TI Dwell-time dependence of the defect accumulation in focused ion beam  
 synthesis of CoSi<sub>2</sub>.  
 AU Bischoff, L.; Hausmann, S.; Voelskow, M.; Teichert, J. (Inst. fuer  
 Ionenstrahlphysik und Materialforschung, Forschungszentrum Rossendorf  
 e.V., Dresden, Germany)  
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam  
 Interactions with Materials and Atoms) (1 Jan. 1999) vol.147, no.1-4,  
 p.327-31. 11 refs.  
 Doc. No.: S0168-583X(98)00533-3  
 Published by: Elsevier  
 Price: CCCC 0168-583X/98/\$19.00  
 CODEN: NIMBEU ISSN: 0168-583X  
 SICI: 0168-583X(19990101)147:1/4L.327:DTDD;1-G  
 Conference: E-MRS 1998 Spring Meeting Symposium J on Ion Implantation into  
 Semiconductors Oxides and Ceramics. Strasbourg, France, 16-19 June 1998  
 Sponsor(s): Council of Eur.; Comm. Eur. Communities  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 45 OF 155 INSPEC (C) 2005 IEE on STN



AN 1999:6141356 INSPEC DN A1999-04-6855-077  
 TI Thin film microstructures produced by nucleation and growth-to-  
 impingement.  
 AU Frost, H.J. (Thayer Sch. of Eng., Dartmouth Coll., Hanover, NH, USA);  
 Thompson, C.V.  
 SO Boundaries and Interfaces in Materials: David A. Smith Symposium.  
 Proceedings of the Memorial Symposium Held at the 1997 TMS Fall Meeting



Editor(s): Pond, R.C.; Clark, W.A.T.; King, A.H.; Williams, D.B.  
 Warrendale, PA, USA: TMS, 1998. p.237-47 of xxxii+348 pp. 86 refs.  
 Conference: Indianapolis, IN, USA, 15-18 Sept 1997  
 Sponsor(s): TMS  
 ISBN: 0-87339-404-6

DT Conference Article  
 TC Theoretical  
 CY United States  
 LA English

L4 ANSWER 46 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1998:6095263 INSPEC DN A9901-6180M-002  
 TI RBS and channeling analysis of **cobalt disilicide** layers produced by  
 focused ion beam implantation.  
 AU Teichert, J.; Voelskow, M.; Bischoff, L.; Hausmann, S. (Inst. fur  
 Ionenstrahlphys. und Materialforschung, Forschungszentrum Rossendorf,  
 Dresden, Germany)  
 SO Vacuum (Oct. 1998) vol.51, no.2, p.261-6. 11 refs.  
 Doc. No.: S0042-207X(98)00171-7  
 Published by: Elsevier  
 Price: CCCC 0042-207X/98/\$19.00+.00  
 CODEN: VACUAV ISSN: 0042-207X  
 SICI: 0042-207X(199810)51:2L.261:CACD;1-P  
 Conference: Vacuum, Electron and Ion Technologies. 10th International  
 Summer School VEIT'97. Varna, Bulgaria, 22-26 Sept 1997  
 DT Conference Article; Journal  
 TC Experimental  
 CY United Kingdom  
 LA English

L4 ANSWER 47 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1998:6048781 INSPEC DN A9822-8115I-008  
 TI **Cobalt disilicide**-induced crystallization of amorphous silicon under  
 XeCl excimer laser irradiation.  
 AU Luby, S.; Majkova, E.; Jergel, M. (Inst. of Phys., Slovak Acad. of Sci.,  
 Bratislava, Slovakia); D'Anna, E.; Luches, A.; Martino, M.; Mengucci, P.;  
 Majni, G.; Dobrocka, E.  
 SO Laser Physics (Jan.-Feb. 1998) vol.8, no.1, p.259-64. 24 refs.  
 Published by: MAIK Nauka/Interperiodica Publishing  
 CODEN: LAPHEJ ISSN: 1054-660X  
 SICI: 1054-660X(199801/02)8:1L.259:CDIC;1-M  
 Conference: Sixth International Workshop on Laser Physics (LPHYS'97).  
 Prague, Czech Republic, 4-8 Aug 1997  
 DT Conference Article; Journal  
 TC Experimental  
 CY Russian Federation  
 LA English

L4 ANSWER 48 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1998:6012198 INSPEC DN A9820-6170T-003; B9810-2550B-019  
 TI Ion beam synthesis of **cobalt disilicide** using focused ion beam  
 implantation.  
 AU Teichert, J.; Bischoff, L.; Hausmann, S. (Inst. fur Ionenstrahlphys. und  
 Materialforschung, Forschungszentrum Rossendorf e.V., Dresden, Germany)

SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (July-Aug. 1998) vol.16, no.4, p.2574-7. 13 refs.  
 Doc. No.: S0734-211X(98)04404-7  
 Published by: AIP for American Vacuum Soc  
 Price: CCCC 0734-211X/98/16(4)/2574(4)/\$15.00  
 CODEN: JVTBD9 ISSN: 0734-211X  
 SICI: 0734-211X(199807/08)16:4L:2574:BSCD;1-L  
 Conference: Japan/US Workshop on Formation of Ion Nanobeams. Osaka, Japan, 16-20 Nov 1997  
 DT Conference Article; Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 49 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text	Links References
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AN 1998:5997835 INSPEC DN A9818-6855-172  
 TI Co-deposition of **cobalt disilicide** on silicon-germanium thin films.  
 AU Goeller, P.T.; Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)  
 SO Thin Solid Films (18 May 1998) vol.320, no.2, p.206-10. 12 refs.  
 Doc. No.: S0040-6090(97)00941-3  
 Published by: Elsevier  
 Price: CCCC 0040-6090/98/\$19.00  
 CODEN: THSFAP ISSN: 0040-6090  
 SICI: 0040-6090(19980518)320:2L:206:DCDS;1-7  
 DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L4 ANSWER 50 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text	Links References
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AN 1998:5963100 INSPEC DN A9816-6822-003  
 TI Structural analysis of buried conducting CoSi<sub>2</sub> layers formed in Si by high-dose Co ion implantation.  
 AU Galayev, A.A. (Inst. of Chem. Problems in Microelectron., Moscow, Russia); Parkhomenko, Yu.N.; Chitchevbatchev, K.D.; Podgorny, D.A.; Belogorohov, A.I.; Dieguez, A.; Romano-Rodriguez, A.; Perez-Rodriguez, A.; Morante, J.R.  
 SO Journal of Crystal Growth (May 1998) vol.187, no.3-4, p.435-43. 11 refs.  
 Doc. No.: S0022-0248(97)00600-3  
 Published by: Elsevier  
 Price: CCCC 0022-0248/98/\$19.00  
 CODEN: JCRGAE ISSN: 0022-0248  
 SICI: 0022-0248(199805)187:3/4L:435:SABC;1-P  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 51 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1998:5946626 INSPEC DN A9815-8115H-001; B9808-0520F-002  
 TI Growth of carbon nanotubes on **cobalt disilicide** precipitates by chemical vapor deposition.  
 AU Mao, J.M.; Sun, L.F.; Qian, L.X.; Pan, Z.W.; Chang, B.H.; Zhou, W.Y.;

Wang, G.; Xie, S.S. (Inst. of Phys., Acad. Sinica, Beijing, China)  
 SO Applied Physics Letters (22 June 1998) vol.72, no.25, p.3297-9. 12 refs.  
 Doc. No.: S0003-6951(98)03625-0  
 Published by: AIP  
 Price: CCCC 0003-6951/98/72(25)/3297(3)/\$15.00  
 CODEN: APPLAB ISSN: 0003-6951  
 SICI: 0003-6951(19980622)72:25L.3297:GCNC;1-7  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 52 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Abstract**  
 AN 1998:5927847 INSPEC DN A9813-6170T-006; B9807-2550B-010  
 TI Dose rate effects in focused ion beam synthesis of **cobalt disilicide**.  
 AU Hausmann, S.; Bischoff, L.; Teichert, J.; Voelskow, M.; Grambole, D.;  
 Herrmann, F.; Moller, W. (Inst. fur Ionenstrahlphys. und  
 Materialforschung, Forschungszentrum Rossendorf, Germany)  
 SO Applied Physics Letters (25 May 1998) vol.72, no.21, p.2719-21. 16 refs.  
 Doc. No.: S0003-6951(98)03421-4  
 Published by: AIP  
 Price: CCCC 0003-6951/98/72(21)/2719(3)/\$15.00  
 CODEN: APPLAB ISSN: 0003-6951  
 SICI: 0003-6951(19980525)72:21L.2719:DREF;1-J  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 53 OF 155 INSPEC (C) 2005 IEE on STN



**Full Text** **Abstract**  
 AN 1998:5908786 INSPEC DN B9806-2550F-046  
 TI Investigation of dwell-time effects on the **cobalt disilicide** formation  
 using focused ion beam implantation.  
 AU Hausmann, S.; Bischoff, L.; Teichert, J.; Grambole, D.; Herrmann, F.;  
 Moller, W. (Inst. fur Ionenstrahlphys. und Materialforschung,  
 Forschungszentrum Rossendorf, Dresden, Germany)  
 SO Microelectronic Engineering (March 1998) vol.41-42, p.233-6. 14 refs.  
 Doc. No.: S0167-9317(98)00053-7  
 Published by: Elsevier  
 Price: CCCC 0167-9317/98/\$19.00  
 CODEN: MIENEF ISSN: 0167-9317  
 SICI: 0167-9317(199803)41/42L.233:IDTE;1-#  
 Conference: Micro- and Nano- Engineering 97. MNE International Conference  
 on Micro- and Nanofabrication. Athens, Greece, 15-18 Sept 1997  
 DT Conference Article; Journal  
 TC Practical; Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 54 OF 155 INSPEC (C) 2005 IEE on STN



**Full Text** **Abstract**  
 AN 1998:5908152 INSPEC DN A9812-6855-007  
 TI Studies of phase formation in CoSi<sub>2</sub> buried layers fabricated using ion  
 implantation.  
 AU Galaev, A.A.; Parkhomenko, Yu.N.; Podgornyi, D.A.; Shcherbachev, K.D.

(Inst. of Steel & Alloys, Moscow, Russia)  
 SO Crystallography Reports (March-April 1998) vol.43, no.2, p.311-16. 8 refs.  
 Published by: MAIK Nauka/Interperiodica Publishing  
 Price: CCCC 1063-7745/98/4302-0311\$15.00  
 CODEN: CYSTE3 ISSN: 1063-7745  
 SICI (Trl): 1063-7745(199803/04)43:2L.311:SPFC;1-X  
 Translation of: Kristallografiya (March-April 1998) vol.43, no.2,  
 p.345-50. 8 refs.  
 CODEN: KRISAJ ISSN: 0023-4761  
 SICI: 0023-4761(199803/04)43:2L.345;1-J  
 DT Journal; Translation Abstracted  
 TC Practical; Experimental  
 CY Russian Federation; Russian Federation  
 LA English



L4 ANSWER 55 OF 155 INSPEC (C) 2005 IEE on STN

   
 AN 1998:5855819 INSPEC DN A9808-6855-096; B9804-2530D-016  
 TI Thin films of CoSi2 co-deposited onto Si1-xGex alloys.  
 AU Goeller, P.T. (Dept. of Mater. Sci. & Eng., North Carolina State Univ.,  
 Raleigh, NC, USA); Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J.  
 SO Structure and Evolution of Surfaces. Symposium  
 Editor(s): Cammarata, R.C.; Chason, E.H.; Einstein, T.L.; Williams, E.D.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.487-92 of xii+509 pp. 23  
 refs.  
 Conference: Boston, MA, USA, 2-5 Dec 1996  
 ISBN: 1-55899-344-4  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 56 OF 155 INSPEC (C) 2005 IEE on STN



   
 AN 1998:5855768 INSPEC DN B9804-2550A-007  
 TI Thermal stability of cobalt and nickel silicides in amorphous and  
 crystalline silicon.  
 AU Poon, M.C. (Dept. of Electr. & Electron. Eng., Hong Kong Univ. of Sci. &  
 Technol., Hong Kong); Deng, F.; Wong, H.; Wong, M.; Sin, J.K.O.; Lan,  
 S.S.; Ho, C.H.; Han, P.G.  
 SO Proceedings. 1997 IEEE HongKong Electron Devices Meeting (Cat.  
 No.97TH8260)  
 New York, NY, USA: IEEE, 1997. p.65-8 of v+160 pp. 7 refs.  
 Conference: Hong Kong, 30 Aug 1997  
 Sponsor(s): IEEE Electron. Devices Soc.; Dept. Electron. Eng. City Univ.  
 Hong Kong  
 ISBN: 0-7803-3802-2  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 57 OF 155 INSPEC (C) 2005 IEE on STN



   
 AN 1998:5825115 INSPEC DN B9803-2550F-058  
 TI Submicrometer patterning of cobaltdisilicide layers by local oxidation.  
 AU Klinkhammer, F.; Dolle, M.; Kappius, L.; Mantl, S. (Inst. fur Schicht- und

Ionentechnik, Forschungszentrum Julich GmbH, Germany)  
 SO Microelectronic Engineering (Nov. 1997) vol.37-38, p.515-21. 8 refs.  
 Doc. No.: S0167-9317(97)00154-8  
 Published by: Elsevier  
 Price: CCCC 0167-9317/97/\$17.00  
 CODEN: MIENEF ISSN: 0167-9317  
 SICI: 0167-9317(199711)37/38L:515:SPCL;1-5  
 Conference: Second European Workshop on Materials for Advanced  
 Metallization. MAM'97. Villard de Lans, France, 16-19 March 1997  
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist.  
 Educ. Nat. Enseignement Superieur  
 DT Conference Article; Journal  
 TC Practical; Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 58 OF 155 INSPEC (C) 2005 IEE on STN

   
 AN 1998:5825112 INSPEC DN B9803-2550F-055  
 TI Arsenic solubility in single crystalline **cobalt disilicide**.  
 AU Mangelinck, D.; Cardenas, J.; Svensson, B.G. (Solid State Electron., R.  
 Inst. of Technol., Stockholm, Sweden)  
 SO Microelectronic Engineering (Nov. 1997) vol.37-38, p.467-73. 20 refs.  
 Doc. No.: S0167-9317(97)00148-2  
 Published by: Elsevier  
 Price: CCCC 0167-9317/97/\$17.00  
 CODEN: MIENEF ISSN: 0167-9317  
 SICI: 0167-9317(199711)37/38L:467:ASSC;1-9  
 Conference: Second European Workshop on Materials for Advanced  
 Metallization. MAM'97. Villard de Lans, France, 16-19 March 1997  
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist.  
 Educ. Nat. Enseignement Superieur  
 DT Conference Article; Journal  
 TC Practical; Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 59 OF 155 INSPEC (C) 2005 IEE on STN

   
 AN 1998:5815922 INSPEC DN A9805-6855-048; B9803-0510D-037  
 TI Thin films of CoSi<sub>2</sub> co-deposited onto Si<sub>1-x</sub>Ge<sub>x</sub> alloys.  
 AU Goeller, P.T. (Dept. of Mater. Sci., North Carolina State Univ., Raleigh,  
 NC, USA); Boyanov, B.I.; Sayers, D.E.; Nemanich, R.J.  
 SO Control of Semiconductor Surfaces and Interfaces. Symposium  
 Editor(s): Prokes, S.M.; Glembocki, O.J.; Brierley, S.K.; Gibson, J.M.;  
 Woodall, J.M.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.365-70 of xiii+505 pp. 23  
 refs.  
 Conference: Boston, MA, USA, 2-5 Dec 1996  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 60 OF 155 INSPEC (C) 2005 IEE on STN

   
 AN 1998:5810079 INSPEC DN A9805-7840-001

TI Color in Pettifor's structure maps: intermetallic compounds for a new use.  
 AU Steinemann, S.G.; Anongba, O.N.B. (Inst. de Phys. Exp., Lausanne Univ., Switzerland); Podloucky, R.  
 SO Journal of Phase Equilibria (Dec. 1997) vol.18, no.6, p.655-62. 48 refs.  
 Published by: ASM Int  
 Price: CCCC 1054-9714/97/\$4.00  
 CODEN: JPEQE6 ISSN: 1054-9714  
 SICI: 1054-9714(199712)18:6L:655:CPSM;1-D  
 Conference: Hume-Rothery Award Symposium held at the TMS Annual Meeting. Las Vegas, NV, USA, 12-16 Feb 1995  
 DT Conference Article; Journal  
 TC General Review; Theoretical; Experimental  
 CY United States  
 LA English

L4 ANSWER 61 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1998:5787851 INSPEC DN A9803-7335-009  
 TI Observation of quantum interference effects in submicron CoSi<sub>2</sub> wires in Si(100).  
 AU Lenssen, D.; Manti, S. (Inst. fur Schicht- und Ionentechnik, Julich, Germany)  
 SO Applied Physics Letters (15 Dec. 1997) vol.71, no.24, p.3540-2. 13 refs.  
 Doc. No.: S0003-6951(97)03150-1  
 Published by: AIP  
 Price: CCCC 0003-6951/97/71(24)/3540/3/\$10.00  
 CODEN: APPLAB ISSN: 0003-6951  
 SICI: 0003-6951(19971215)71:24L:3540:OQIE;1-9  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 62 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1997:5780387 INSPEC DN A9802-6460-008; B9801-2550F-099  
 TI Local nucleation and lateral crystallisation of the silicide phases in CoSi<sub>2</sub> buffer layer of YBCO/CoSi<sub>2</sub>/Si structure.  
 AU Belousov, I.; Rudenko, E. (Inst. of Mater. Phys., Acad. of Sci., Kiev, Ukraine); Linzen, S.; Seidel, P.  
 SO European Workshop. Materials for Advanced Metallization. MAM'97 Abstracts Booklet (IEEE Cat. No.97TH8287)  
 Paris, France: Soc. Francaise du Vide, 1997. p.185-8 of 221 pp. 6 refs.  
 Conference: Villard de Lans, France, 16-19 March 1997  
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist. Educ. Nat. Enseignement Superieur  
 DT Conference Article  
 TC Application; Experimental  
 CY France  
 LA English

L4 ANSWER 63 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1997:5780375 INSPEC DN B9801-2550F-090  
 TI Arsenic solubility in single crystalline **cobalt disilicide**.  
 AU Mangelinck, D.; Cardenas, J.; Svensson, B.G. (Solid State Electron., R. Inst. of Technol., Stockholm, Sweden)

SO European Workshop. Materials for Advanced Metallization. MAM'97 Abstracts Booklet (IEEE Cat. No.97TH8287)  
 Paris, France: Soc. Francaise du Vide, 1997. p.120-1 of 221 pp. 5 refs.  
 Conference: Villard de Lans, France, 16-19 March 1997  
 Sponsor(s): Int. Union for Vacuum Sci., Tech. & Applications; Minist. Educ. Nat. Enseignement Superieur  
 DT Conference Article  
 TC Practical; Experimental  
 CY France  
 LA English

L4 ANSWER 64 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1997:5744591 INSPEC DN A9724-7340N-003; B9712-2550F-028  
 TI Quantum transport in ion beam synthesized **cobalt disilicide** wires.  
 AU Lenssen, D.; Mesters, S.; Mantl, S. (Inst. for Thin Film & Ion Technol., Forschungszentrum Julich GmbH, Germany)  
 SO Materials Modification and Synthesis by Ion Beam Processing. Symposium  
 Editor(s): Alexander, D.E.; Cheung, N.W.; Park, B.; Skorupa, W.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.295-300 of xix+727 pp. 9 refs.  
 Conference: Boston, MA, USA, 2-5 Dec 1996  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 65 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text Available

AN 1997:5681147 INSPEC DN A9719-2940-055; B9710-7420-026  
 TI Fabrication of an integrated Delta E-E-silicon detector by wafer bonding using **cobalt disilicide**.  
 AU Thungstroem, G. (Dept. of Inf. Technol., Mid-Sweden Univ., Sundsvall, Sweden); van Veldhuizen, E.J.; Westerberg, L.; Norlin, L.-O.; Petersson, C.S.  
 SO Nuclear Instruments & Methods in Physics Research, Section A (Accelerators, Spectrometers, Detectors and Associated Equipment) (1 June 1997) vol.391, no.2, p.315-28. 13 refs.  
 Doc. No.: S0168-9002(97)00408-7  
 Published by: Elsevier  
 Price: CCCC 0168-9002/97/\$17.00  
 CODEN: NIMAER ISSN: 0168-9002  
 SICI: 0168-9002(19970601)391:2L:315:FISD;1-B  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 66 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1997:5664390 INSPEC DN B9709-2550F-042  
 TI Silicidation strategy of sub-0.1 mu m junctions for deep submicron devices.  
 AU Jiunn-Yann Tsai; Osburn, C.M. (Dept. of Electr. & Comput. Eng., North Carolina State Univ., Raleigh, NC, USA); Hsia, S.L.  
 SO Silicide Thin Films - Fabrication, Properties, and Applications. Symposium  
 Editor(s): Tung, R.T.; Maex, K.; Pellegrini, P.W.; Allen, L.H.

Pittsburgh, PA, USA: Mater. Res. Soc, 1996. p.245-50 of xv+648 pp. 19 refs.

Conference: Boston, MA, USA, 27-30 Nov 1995

DT Conference Article

TC Practical

CY United States

LA English

L4 ANSWER 67 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5657371 INSPEC DN A9718-8115G-020; B9709-0510D-130

TI Epitaxial films of **cobalt disilicide** (100) evaporated onto Si (100) from a mixed source.

AU Goeller, P.T.; Wang, Z.; Sayers, D.E.; Glass, J.T.; Nemanich, R.J. (Dept. of Phys., North Carolina State Univ., Raleigh, NC, USA)

SO Silicide Thin Films - Fabrication, Properties, and Applications. Symposium Editor(s): Tung, R.T.; Maex, K.; Pellegrini, P.W.; Allen, L.H. Pittsburgh, PA, USA: Mater. Res. Soc, 1996. p.511-16 of xv+648 pp. 12 refs.

Conference: Boston, MA, USA, 27-30 Nov 1995

DT Conference Article

TC Experimental

CY United States

LA English

L4 ANSWER 68 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5534859 INSPEC DN A9709-6822-017; B9705-0510D-086

TI Co silicide formation on SiGeC/Si and SiGe/Si layers.

AU Donaton, R.A.; Maex, K. (IMEC, Leuven, Belgium); Vantomme, A.; Langouche, G.; Morciaux, Y.; St. Amour, A.; Sturm, J.C.

SO Applied Physics Letters (10 March 1997) vol.70, no.10, p.1266-8. 13 refs. Doc. No.: S0003-6951(97)00610-4

Published by: AIP

Price: CCCC 0003-6951/97/70(10)/1266/3/\$10.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19970310)70:10L:1266:SFSS;1-J

DT Journal

TC Practical; Experimental

CY United States

LA English

L4 ANSWER 69 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5530238 INSPEC DN A9709-7475-002; B9705-3220-005

TI **Cobalt disilicide** buffer layer for YBCO film on silicon.

AU Belousov, I.; Rudenko, E. (Inst. of Phys. of Metals, Acad. of Sci., Kiev, Ukraine); Linzen, S.; Seidel, P.

SO Journal of Low Temperature Physics (Feb. 1997) vol.106, no.3-4, p.433-8. 9 refs.

Published by: Plenum

Price: CCCC 0022-2291/97/0200-0433\$12.50/0

CODEN: JLTPAC ISSN: 0022-2291

SICI: 0022-2291(199702)106:3/4L:433:CDBL;1-#

Conference: Weak Superconductivity Symposium. Smolenice Castle, Slovakia, 4-7 Aug 1996

DT Conference Article; Journal



TC Experimental  
CY United States  
LA English

L4 ANSWER 70 OF 155 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text Available

AN 1996:5459760 INSPEC DN A9703-8115N-003  
TI Diffusing species and growth interfaces during **cobalt disilicide** formation.  
AU Comrie, C.M. (Cape Town Univ., Rondebosch, South Africa)  
SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (Sept. 1996) vol.118, no.1-4, p.119-22. 12 refs.  
Published by: Elsevier  
Price: CCCC 0168-583X/96/\$15.00  
CODEN: NIMBEU ISSN: 0168-583X  
SICI: 0168-583X(199609)118:1/4L:119:DSGI;1-8  
Conference: Ion Beam Analysis. Twelfth International Conference. Tempe, AZ, USA, 22-26 May 1995  
Sponsor(s): Arizona State Univ.; Bohmische Soc.; et al  
DT Conference Article; Journal  
TC Experimental  
CY Netherlands  
LA English

L4 ANSWER 71 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1996:5382948 INSPEC DN A9621-6630J-002  
TI Solid solubility and diffusion of boron in single-crystalline **cobalt disilicide**.  
AU Zaring, C.; Pisch, A.; Cardenas, J. (R. Inst. of Technol., Stockholm, Sweden); Gas, P.; Svensson, B.G.  
SO Journal of Applied Physics (1 Sept. 1996) vol.80, no.5, p.2742-8. 35 refs.  
Doc. No.: S0021-8979(96)06117-8  
Published by: AIP  
Price: CCCC 0021-8979/96/80(5)/2742/7/\$10.00  
CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(19960901)80:5L:2742:SSDB;1-H  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 72 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1996:5340719 INSPEC DN B9609-2560H-008  
TI Self-aligned **cobalt disilicide**/silicon Schottky barrier diodes.  
AU Woods, N.J.; Hall, S. (Dept. of Electr. Eng. & Electron., Liverpool Univ., UK)  
SO ESSDERC '95. Proceedings of the 25th European Solid State Device Research Conference  
Editor(s): de Graaff, H.C.; van Kranenburg, H.  
Gif sur Yvette, France: Editions Frontieres, 1995. p.517-20 of xlv+847 pp. 5 refs.  
Conference: The Hague, Netherlands, 25-27 Sept 1995  
Sponsor(s): Philips Semicond.; EU; ASM-Lithography; Appl. Mater.; GSM Nederland; ASM Int.; Novellus Syst.; Philips Machine Factories et al

ISBN: 2-86332-182-X

DT Conference Article  
TC Practical; Theoretical; Experimental  
CY France  
LA English

L4 ANSWER 73 OF 155 INSPEC (C) 2005 IEE on STN



AN 1996:5320634 INSPEC DN A9616-7340N-006; B9608-2530D-020  
TI Self-aligned **cobalt disilicide**/silicon Schottky barrier contacts:  
fabrication, materials and electrical characterization.  
AU Woods, N.J.; Hall, S. (Dept. of Electr. Eng. & Electron., Liverpool Univ.,  
UK)  
SO Semiconductor Science and Technology (July 1996) vol.11, no.7, p.1103-15.  
21 refs.  
Published by: IOP Publishing  
Price: CCCC 0268-1242/96/071103+13\$19.50  
CODEN: SSTEET ISSN: 0268-1242  
SICI: 0268-1242(199607)11:7L.1103:SACD;1-E  
DT Journal  
TC Experimental  
CY United Kingdom  
LA English

L4 ANSWER 74 OF 155 INSPEC (C) 2005 IEE on STN



AN 1996:5314473 INSPEC DN B9608-2575-069  
TI **Cobalt disilicide** interconnects for micromechanical devices.  
AU Teichert, J.; Bischoff, L.; Hesse, E.; Schneider, P.; Panknin, D. (Inst.  
of Ion Beam Phys., Res. Centre Rossendorf Inc., Dresden, Germany);  
Gessner, T.; Lobner, B.; Zichner, N.  
SO Journal of Micromechanics and Microengineering (June 1996) vol.6, no.2,  
p.272-8. 17 refs.  
Published by: IOP Publishing  
Price: CCCC 0960-1317/96/020272+07\$19.50  
CODEN: JMMIEZ ISSN: 0960-1317  
SICI: 0960-1317(199606)6:2L.272:CDIM;1-P  
DT Journal  
TC Experimental  
CY United Kingdom  
LA English

L4 ANSWER 75 OF 155 INSPEC (C) 2005 IEE on STN



AN 1996:5301972 INSPEC DN A9615-7125R-001  
TI Electronic structure of a buried NiSi<sub>2</sub> or CoSi<sub>2</sub> layer in bulk Si.  
AU Schick, J.T. (Dept. of Phys., Villanova Univ., PA, USA); Bose, S.M.  
SO Physical Review B (Condensed Matter) (15 May 1996) vol.53, no.19,  
p.12609-12. 21 refs.  
Doc. No.: S0163-1829(96)09119-9  
Published by: APS through AIP  
Price: CCCC 0163-1829/96/53(19)/12609(4)\$10.00  
CODEN: PRBMDO ISSN: 0163-1829  
SICI: 0163-1829(19960515)53:19L.12609:ESBN;1-N  
DT Journal  
TC Experimental  
CY United States

LA English

L4 ANSWER 76 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1996:5183907 INSPEC DN A9605-8115I-011; B9603-0520F-061  
 TI Study of WSi<sub>2</sub> and CoSi<sub>2</sub> thin films deposited by laser ablation.  
 AU Glebovsky, V.G.; Ermolov, S.N.; Oganyan, R.A.; Stinov, E.D. (Inst. of Solid State Phys., Acad. of Sci., Chernogolovka, Russia)  
 SO Beam-Solid Interactions for Materials Synthesis and Characterization. Symposium  
 Editor(s): Jacobson, D.C.; Luzzi, D.E.; Heinz, T.F.; Iwaki, M.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1995. p.659-64 of xv+746 pp. 4 refs.  
 Conference: Boston, MA, USA, 28 Nov-2 Dec 1994  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 77 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1996:5173528 INSPEC DN A9605-6822-004; B9603-2550F-023  
 TI Dominant diffusing species during cobalt silicide formation.  
 AU Comrie, M.; Newman, R.T. (Cape Town Univ., Rondebosch, South Africa)  
 SO Journal of Applied Physics (1 Jan. 1996) vol.79, no.1, p.153-6. 18 refs.  
 Published by: AIP  
 Price: CCCC 0021-8979/96/79(1)/153/4/\$6.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 SICI: 0021-8979(19960101)79:1L:153:DDSD;1-X  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 78 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:5135159 INSPEC DN A9602-6855-044  
 TI Formation of CoSi<sub>2</sub> on strained Si<sub>0.8</sub>Ge<sub>0.2</sub> using a sacrificial Si layer.  
 AU Donaton, R.A.; Kolodinski, S.; Caymax, M.; Roussel, P.; Bender, H.; Brijs, B.; Maex, K. (IMEC, Leuven, Belgium)  
 SO Applied Surface Science (Oct. 1995) vol.91, p.77-81. 12 refs.  
 Price: CCCC 0169-4332/95/\$09.50  
 CODEN: ASUSEE ISSN: 0169-4332  
 Conference: MAM 1995. First European Workshop on Materials for Advanced Metallization. Radebeul, Germany, 19-22 March 1995  
 Sponsor(s): Bundesministerium fur Bildung, Wissenschaft, Forschung und Technol.; SIEMANS AG; Appl. Mater. GmbH; et al  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 79 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:5111333 INSPEC DN A9524-7340N-012; B9512-2530D-033  
 TI CoSi<sub>2</sub> ohmic contacts to n-type 6H-SiC.  
 AU Lundberg, N.; Ostling, M. (Dept. of Electron., R. Inst. of Technol.,

Stockholm, Sweden)

SO Solid-State Electronics (Dec. 1995) vol.38, no.12, p.2023-8. 30 refs.  
 Price: CCCC 0038-1101/95/\$9.50+0.00  
 CODEN: SSELAS ISSN: 0038-1101  
 DT Journal  
 TC Experimental  
 CY United Kingdom  
 LA English

L4 ANSWER 80 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:5108958 INSPEC DN B9512-2560H-016  
 TI One micrometre scale self-aligned **cobalt disilicide** Schottky barrier diodes.  
 AU Woods, N.J.; Hall, S. (Dept. of Electr. Eng. & Electron., Liverpool Univ., UK)  
 SO Electronics Letters (12 Oct. 1995) vol.31, no.21, p.1878-80. 4 refs.  
 Price: CCCC 0013-5194/95/\$10.00  
 CODEN: ELLEAK ISSN: 0013-5194  
 DT Journal  
 TC Experimental  
 CY United Kingdom  
 LA English

L4 ANSWER 81 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:5092532 INSPEC DN A9523-7125P-002  
 TI Anisotropy of electronic distribution in a **cobalt disilicide** single crystal.  
 AU Bellin, C.; Loupias, G. (Lab. de Miner.-Cristallogr., Paris VI Univ., France); Manuel, A.A.; Jarlborg, T.; Sakurai, Y.; Tanaka, Y.; Shiotani, N.  
 SO Solid State Communications (Nov. 1995) vol.96, no.8, p.563-7. 28 refs.  
 Price: CCCC 0038-1098/95/\$9.50+0.00  
 CODEN: SSCO44 ISSN: 0038-1098  
 DT Journal  
 TC Theoretical; Experimental  
 CY United States  
 LA English

L4 ANSWER 82 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1995:5053984 INSPEC DN A9520-6822-020; B9511-0510D-018  
 TI Layer reversal of Co/Zr bilayer and epitaxial growth of CoSi<sub>2</sub> layer on Si(001) substrate.  
 AU Jeong Soo Byun; Jae Jeong Kim; Woo Shik Kim (ULSI Lab., LG Semicon Co. Ltd., Cheongju, South Korea); Hyeong Joon Kim  
 SO Journal of the Electrochemical Society (Aug. 1995) vol.142, no.8, p.2805-12. 25 refs.  
 Price: CCCC 0013-4651/95/\$5.00+0.00  
 CODEN: JESOAN ISSN: 0013-4651  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 83 OF 155 INSPEC (C) 2005 IEE on STN



AN 1995:5051601 INSPEC DN A9520-6150C-004  
 TI Analysis of crystal nucleation and growth in amorphous **cobalt disilicide**.  
 AU Smith, D.A. (Stevens Inst. of Technol., Hoboken, NJ, USA); Evans, P.V.;  
 Koppikar, S.R.  
 SO Crystallization and Related Phenomena in Amorphous Materials. Symposium  
 Editor(s): Libera, M.; Haynes, T.E.; Cebe, P.; Dickinson, J.E., Jr.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1994. p.271-82 of xv+755 pp. 9 refs.  
 Conference: Boston, MA, USA, 29 Nov-2 Dec 1993  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 84 OF 155 INSPEC (C) 2005 IEE on STN



AN 1995:5047860 INSPEC DN A9520-7340N-002; B9510-2530D-023  
 TI Low-temperature processing of shallow junctions using epitaxial and  
 polycrystalline CoSi<sub>2</sub>.  
 AU Jones, E.C.; Cheung, N.W. (Dept. of Electr. Eng. & Comput. Sci.,  
 California Univ., Berkeley, CA, USA); Fraser, D.B.  
 SO Journal of Electronic Materials (July 1995) vol.24, no.7, p.863-73. 30  
 refs.  
 CODEN: JECMA5 ISSN: 0361-5235  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 85 OF 155 INSPEC (C) 2005 IEE on STN



AN 1995:5037385 INSPEC DN A9519-6855-043  
 TI Entropic origin of the free energy barrier to nucleation of crystallites  
 in amorphous CoSi<sub>2</sub> thin films.  
 AU Shi, F.G. (Dept. of Chem. Eng., California Univ., Irvine, CA, USA); Tu,  
 K.N.  
 SO Physical Review Letters (29 May 1995) vol.74, no.22, p.4476-8. 12 refs.  
 Price: CCCC 0031-9007/95/74(22)/4476(3)\$06.00  
 CODEN: PRLTAO ISSN: 0031-9007  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 86 OF 155 INSPEC (C) 2005 IEE on STN



AN 1995:5024444 INSPEC DN A9518-8160B-007; B9510-2550E-006  
 TI Etching of CoSi<sub>2</sub> in HF-based solutions.  
 AU Donaton, R.A.; Lokere, K.; Verbeeck, R.; Maex, K. (IMEC, Leuven, Belgium)  
 SO Applied Surface Science (July 1995) vol.89, no.3, p.221-7. 4 refs.  
 Price: CCCC 0169-4332/95/\$09.50  
 CODEN: ASUSEE ISSN: 0169-4332  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 87 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1995:4990703 INSPEC DN A9515-6848-004  
 TI Diffuse X-ray scattering from thin films with defects.  
 AU Bahr, D.; Press, W. (Inst. fur Experimentalphys., Kiel Univ., Germany);  
 Jebasinski, R.; Mantl, S.  
 SO Physical Review B (Condensed Matter) (1 May 1995) vol.51, no.18,  
 p.12223-7. 23 refs.  
 Price: CCCC 0163-1829/95/51(18)/12223(5)/\$6.00  
 CODEN: PRBMDO ISSN: 0163-1829  
 DT Journal  
 TC Theoretical  
 CY United States  
 LA English

L4 ANSWER 88 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1995:4940117 INSPEC DN A9510-7330-007; B9506-2530D-025  
 TI Buried Schottky contacts in patterned cobalt silicide layers in silicon  
 using wafer bonding.  
 AU Thungstrom, G.; Frojdh, C.; Petersson, C.S. (Dept. of Solid State  
 Electron., R. Inst. of Technol., Kista, Sweden)  
 SO Advanced Metallization for Devices and Circuits - Science, Technology and  
 Manufacturability Symposium  
 Editor(s): Murarka, S.P.; Katz, A.; Tu, K.N.; Maex, K.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1994. p.475-80 of xiv+768 pp. 6  
 refs.  
 Conference: San Francisco, CA, USA, 4-8 April 1994  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 89 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1994:4837860 INSPEC DN A9502-7340N-008; B9501-2530D-017  
 TI Cobalt disilicide (CoSi<sub>2</sub>) Schottky contacts to 6H-SiC.  
 AU Lundberg, N.; Ostling, M. (Dept. of Electron., R. Inst. of Technol.,  
 Stockholm, Sweden)  
 SO Physica Scripta Volume T (1994) vol.T54, p.273-7. 13 refs.  
 CODEN: PHSTBO ISSN: 0281-1847  
 Conference: 16th Nordic Semiconductor Meeting. Laugarvatn, Iceland, 12-15  
 June 1994  
 DT Conference Article; Journal  
 TC Experimental  
 CY Sweden  
 LA English

L4 ANSWER 90 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1994:4837850 INSPEC DN B9501-2560J-021  
 TI Process optimisation and characterisation of PBT structures.  
 AU Hatzikonstantinidou, S.; Nilsson, H.-E.; Frojdh, C.; Petersson, C.S.  
 (Dept. of Solid State Electron., R. Inst. of Technol., Stockholm, Sweden)  
 SO Physica Scripta Volume T (1994) vol.T54, p.226-9. 10 refs.

CODEN: PHSTBO ISSN: 0281-1847

Conference: 16th Nordic Semiconductor Meeting. Laugarvatn, Iceland, 12-15 June 1994

DT Conference Article; Journal  
TC Practical; Experimental  
CY Sweden  
LA English

L4 ANSWER 91 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4837815 INSPEC DN B9501-2550-006

TI Contacts to monocrystalline n- and p-type silicon by wafer bonding using **cobalt disilicide**.

AU Thungstrom, G.; Frojdh, C.; Svedberg, P.; Petersson, C.S. (Dept. of Solid State Electron., R. Inst. of Technol., Kista, Sweden)

SO Physica Scripta Volume T (1994) vol.T54, p.77-80. 4 refs.

CODEN: PHSTBO ISSN: 0281-1847

Conference: 16th Nordic Semiconductor Meeting. Laugarvatn, Iceland, 12-15 June 1994

DT Conference Article; Journal  
TC Practical  
CY Sweden  
LA English

L4 ANSWER 92 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4810422 INSPEC DN A9424-6855-038

TI Non-destructive characterization of the uniformity of thin **cobalt disilicide** films by Raman microprobe measurements.

AU Perez-Rodriguez, A. (Dept. de Fisica Aplicada i Electron., Barcelona Univ., Spain); Roca, E.; Jawhari, T.; Morante, J.R.; Schreutelkamp, R.J.

SO Thin Solid Films (15 Oct. 1994) vol.251, no.1, p.45-50. 11 refs.

Price: CCCC 0040-6090/94/\$7.00

CODEN: THSFAP ISSN: 0040-6090

DT Journal  
TC Experimental  
CY Switzerland  
LA English

L4 ANSWER 93 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4764029 INSPEC DN A9420-8115L-019

TI Deposition of **cobalt disilicide** thin films by laser ablation of cast targets.

AU Glebovsky, V.G.; Oganyan, R.A.; Ermolov, S.N. (Inst. of Solid State Phys., Chernogolovka, Russia); Kolosova, E.V.

SO Thin Solid Films (15 Aug. 1994) vol.248, no.2, p.145-8. 9 refs.

Price: CCCC 0040-6090/94/\$7.00

CODEN: THSFAP ISSN: 0040-6090

DT Journal  
TC Experimental  
CY Switzerland  
LA English

L4 ANSWER 94 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4762766 INSPEC DN A9420-8140N-065; C9410-7320-136  
 TI Materials science from first-principles: CoSi<sub>2</sub> surfaces.  
 AU Vogtenhuber, D.; Podloucky, R. (Inst. fur Phys. Chem., Wien Univ., Austria); Steinemann, S.G.  
 SO Cray Channels (1994) vol.16, no.1, p.22-5. 6 refs.  
 CODEN: CRCHE8  
 DT Journal  
 TC Practical  
 CY United States  
 LA English

L4 ANSWER 95 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Abstract**  
 AN 1994:4749596 INSPEC DN A9419-6320D-013  
 TI Ground-state properties of CoSi<sub>2</sub> determined by a total-energy pseudopotential method.  
 AU Milman, V. (Div. of Solid State, Oak Ridge Nat. Lab., TN, USA); Lee, M.H.; Payne, M.C.  
 SO Physical Review B (Condensed Matter) (15 June 1994) vol.49, no.23, p.16300-8. 42 refs.  
 Price: CCCC 0163-1829/94/49(23)/16300(9)/\$6.00  
 CODEN: PRBMDO ISSN: 0163-1829  
 DT Journal  
 TC Theoretical  
 CY United States  
 LA English

L4 ANSWER 96 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Abstract**  
 AN 1994:4735635 INSPEC DN B9409-2560H-031  
 TI Mixed Schottky/p-n junction behavior in diodes produced by outdiffusion from polycrystalline **cobalt disilicide**.  
 AU Foty, D. (IBM Corp., Essex Junction, VT, USA); Hanafi, H.; Agnello, P.; Ho, H.  
 SO International Electron Devices Meeting 1992. Technical Digest (Cat. No.92CH3211-0)  
 New York, NY, USA: IEEE, 1992. p.841-4 of 1022 pp. 10 refs.  
 Conference: San Francisco, CA, USA, 13-16 Dec 1992  
 Sponsor(s): Electron Devices Soc. IEEE  
 Price: CCCC 0 7803 0817 4/92/\$3.00  
 ISBN: 0-7803-0817-4  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 97 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Abstract**  
 AN 1994:4723027 INSPEC DN A9418-7865-009  
 TI Optical Properties of buried **cobalt disilicide** layers in silicon.  
 AU Lu, F.; Perry, C.H. (Dept. of Phys., Northeastern Univ., Boston, MA, USA); Namavar, F.  
 SO Journal of Applied Physics (1 June 1994) vol.75, no.11, p.7465-9. 11 refs.  
 Price: CCCC 0021-8979/94/75(11)/7465/5/\$6.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental



CY United States  
LA English

L4 ANSWER 98 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Index**

AN 1994:4710320 INSPEC DN A9416-6170J-006  
TI Imaging misfit dislocations in epitaxial CoSi<sub>2</sub>/Si(111) layers using quantum size microscopy.  
AU Kubby, J.A.; Greene, W.J. (Xerox Webster Res. Center, NY, USA)  
SO Surface Science (20 May 1994) vol.311, no.3, p.L695-702. 27 refs.  
Price: CCCC 0039-6028/94/\$07.00  
CODEN: SUSCAS ISSN: 0039-6028  
DT Journal  
TC Experimental  
CY Netherlands  
LA English

L4 ANSWER 99 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Index**

AN 1994:4665371 INSPEC DN B9406-4250-015  
TI **Cobalt disilicide** intercell ohmic contacts for multijunction photovoltaic energy converters.  
AU Kalkhoran, N.M.; Maruska, H.P.; Namavar, F. (Spire Corp., Bedford, MA, USA)  
SO Applied Physics Letters (11 April 1994) vol.64, no.15, p.1980-2. 16 refs.  
Price: CCCC 0003-6951/94/64(15)/1980/3/\$6.00  
CODEN: APPLAB ISSN: 0003-6951  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 100 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Index**

AN 1994:4652798 INSPEC DN A9411-6855-040  
TI Non-destructive thickness determination of thin cobalt and **cobalt disilicide** layers on silicon substrates.  
AU Roca, E. (Fac. de Fisica, Barcelona Univ., Spain); Vanhellefont, J.; Schreutelkamp, R.J.; Vermeiren, J.  
SO Thin Solid Films (15 March 1994) vol.240, no.1-2, p.110-13. 6 refs.  
Price: CCCC 0040-6090/94/\$7.00  
CODEN: THSFAP ISSN: 0040-6090  
DT Journal  
TC Experimental  
CY Switzerland  
LA English

L4 ANSWER 101 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text** **Index**

AN 1994:4649855 INSPEC DN A9411-6630J-001; B9406-2550B-005  
TI Solid source diffusion from agglomerating silicide sources. I. Measurement and modeling.  
AU Tsai, J.Y.; Canovai, C. (Dept. of Electr. & Comput. Eng., North Carolina State Univ., Raleigh, NC, USA); Osburn, C.M.; Wang, Q.F.; Rose, J.; Cowen, A.; Denker, M.S.  
SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer

Structures) (Jan.-Feb. 1994) vol.12, no.1, p.219-29. 46 refs.

Price: CCCC 0734-211X/94/12(1)/219/11/\$1.00

CODEN: JVTBD9 ISSN: 0734-211X

Conference: Second International Workshop on the Measurement and Characterization of Ultra-Shallow Doping Profiles in Semiconductors. Research Triangle Park, NC, USA, 23-25 March 1993

Sponsor(s): MCNC; NIST; American Vacuum Soc.; Office of Naval Res

DT Conference Article; Journal

TC Theoretical; Experimental

CY United States

LA English

L4 ANSWER 102 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4649853 INSPEC DN B9406-2550F-004

TI Secondary ion mass spectrometry measurements of shallow boron profiles in cobalt, silicon, and **cobalt disilicide**.

AU Mohadjeri, B.; Svensson, B.G. (R. Inst. of Technol., Stockholm, Sweden)

SO Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (Jan.-Feb. 1994) vol.12, no.1, p.209-13. 15 refs.

Price: CCCC 0734-211X/94/12(1)/209/5/\$1.00

CODEN: JVTBD9 ISSN: 0734-211X

Conference: Second International Workshop on the Measurement and Characterization of Ultra-Shallow Doping Profiles in Semiconductors. Research Triangle Park, NC, USA, 23-25 March 1993

Sponsor(s): MCNC; NIST; American Vacuum Soc.; Office of Naval Res

DT Conference Article; Journal

TC Theoretical; Experimental

CY United States

LA English

L4 ANSWER 103 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4636603 INSPEC DN A9409-6822-023; B9405-2550F-053

TI Agglomeration-free nanoscale cobalt silicide film formation via substrate preamorphization.

AU Pramanick, S.; Patnaik, B.K.; Rozgonyi, G.A. (Dept. of Mater. Sci. & Eng., North Carolina State Univ., Raleigh, NC, USA)

SO Materials Reliability in Microelectronics III Symposium

Editor(s): Rodbell, K.P.; Filter, W.F.; Frost, H.J.; Ho, P.S.

Pittsburgh, PA, USA: Mater. Res. Soc, 1993. p.475-80 of xi+496 pp. 8 refs.

Conference: San Francisco, CA, USA, 12-15 April 1993

DT Conference Article

TC Experimental

CY United States

LA English

L4 ANSWER 104 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4619798 INSPEC DN A9408-8160B-023; B9404-2550F-028

TI Kinetics of the formation of **cobalt disilicide** at high temperature under rapid electron beam heating.

AU Warris, J.; Suleman, M. (Centre for Solid State Phys., Punjab Univ., Lahore, Pakistan); Mahmood, F.; Ahmed, H.

SO Journal of Materials Science Letters (15 Jan. 1994) vol.13, no.2, p.96-8. 13 refs.

CODEN: JMSLD5 ISSN: 0261-8028

DT Journal  
 TC Experimental  
 CY United Kingdom  
 LA English

L4 ANSWER 105 OF 155 INSPEC (C) 2005 IEE on STN



AN 1994:4599108 INSPEC DN A9406-6855-051  
 TI Microstructural studies of epitaxial CoSi<sub>2</sub> layers on silicon produced by ion beam synthesis and rapid thermal annealing.  
 AU Meekison, C.D.; Booker, G.R. (Dept. of Mater., Oxford Univ., UK); Reeson, K.J.; Spraggs, R.S.; Gwilliam, R.M.; Sealy, B.J.  
 SO Journal of Applied Physics (15 Dec. 1993) vol.74, no.12, p.7129-33. 19 refs.  
 Price: CCCC 0021-8979/93/74(12)/7129/5/\$6.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 106 OF 155 INSPEC (C) 2005 IEE on STN



AN 1993:4531369 INSPEC DN A9401-6170A-003; B9401-2550B-008  
 TI Annealing of silicon implanted by a high dose of cobalt ions investigated by in situ X-ray diffraction.  
 AU Muller, M.; Bahr, D.; Press, W. (Inst. fur Experimentalphys., Kiel Univ., Germany); Jevasinski, R.; Mantl, S.  
 SO Journal of Applied Physics (1 Aug. 1993) vol.74, no.3, p.1590-6. 27 refs.  
 Price: CCCC 0021-8979/93/74(3)/1590/7/\$6.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 107 OF 155 INSPEC (C) 2005 IEE on STN



AN 1993:4469978 INSPEC DN B9310-2560R-036  
 TI **Cobalt disilicide** as dopant diffusion source for polysilicon gates in MOS devices.  
 AU Lin, J.; Chen, W.; Banerjee, S.; Lee, J. (Microelectron. Res. Center, Texas Univ., Austin, TX, USA); Magee, C.  
 SO Journal of Electronic Materials (June 1993) vol.22, no.6, p.667-73. 25 refs.  
 CODEN: JECMA5 ISSN: 0361-5235  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 108 OF 155 INSPEC (C) 2005 IEE on STN



AN 1993:4463722 INSPEC DN A9318-6822-030; B9309-2550F-072  
 TI Stability of nanoscale cobalt silicide film formation on polysilicon.  
 AU Pramanick, S.; Erokhin, Yu.N.; Patnaik, B.K.; Rozgonyi, G.A. (North

Carolina State Univ., Raleigh, NC, USA); Gambino, J.P.  
 SO Advanced Metallization and Processing for Semiconductor Devices and  
 Circuits - II. Symposium  
 Editor(s): Katz, A.; Murarka, S.P.; Nissim, Y.I.; Harper, J.M.E.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1992. p.435-40 of xvii+965 pp. 8  
 refs.  
 Conference: San Francisco, CA, USA, 27 April-1 May 1992  
 Sponsor(s): AT&T Bell Lab.; A.G. Associates; Air Products & Chem.; et al  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 109 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1993:4463679 INSPEC DN B9309-2550F-054  
 TI Thermal stability of **cobalt disilicide** for self-aligned silicide  
 applications.  
 AU Chen, W.; Lin, J.; Banerjee, S.; Lee, J. (Dept. of Electr. & Comput. Eng.,  
 Texas Univ., Austin, TX, USA)  
 SO Advanced Metallization and Processing for Semiconductor Devices and  
 Circuits - II. Symposium  
 Editor(s): Katz, A.; Murarka, S.P.; Nissim, Y.I.; Harper, J.M.E.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1992. p.163-7 of xvii+965 pp. 8  
 refs.  
 Conference: San Francisco, CA, USA, 27 April-1 May 1992  
 Sponsor(s): AT&T Bell Lab.; A.G. Associates; Air Products & Chem.; et al  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 110 OF 155 INSPEC (C) 2005 IEE on STN

**Full Text**

AN 1993:4383094 INSPEC DN A9310-6170T-007; B9305-2550B-034  
 TI Dependence of buried CoSi<sub>2</sub> resistivity on ion implantation and annealing  
 conditions.  
 AU Namavar, F.; Kalkhoran, N.M.; Manke, J.M. (Spire Corp., Bedford, MA, USA);  
 Luo, L.; McGinn, J.T.  
 SO Phase Formation and Modification by Beam-Solid Interactions Symposium  
 Editor(s): Was, G.S.; Rehn, L.E.; Follstaedt, D.M.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1992. p.285-92 of xix+913 pp. 13  
 refs.  
 Conference: Boston, MA, USA, 2-6 Dec 1991  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 111 OF 155 INSPEC (C) 2005 IEE on STN

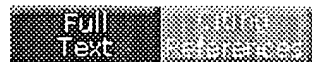
**Full Text**

AN 1993:4337133 INSPEC DN A9306-6855-002; B9303-2550-016  
 TI Improved stability of thin **cobalt disilicide** films using BF<sub>2</sub> implantation.  
 AU Wang, Q.F.; Tsai, J.Y. (Dept. of Electr. & Comput. Eng., North Carolina  
 State Univ., Raleigh, NC, USA); Osburn, C.M.; Chapman, R.; McGuire, G.E.  
 SO Applied Physics Letters (14 Dec. 1992) vol.61, no.24, p.2920-2. 15 refs.  
 Price: CCCC 0003-6951/92/492920-03\$03.00

CODEN: APPLAB ISSN: 0003-6951

DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 112 OF 155 INSPEC (C) 2005 IEE on STN



AN 1992:4253694 INSPEC DN A9222-6855-027

TI Stress measurements on vacuum evaporated cobalt silicide films on silicon substrates.

AU Aloupojannis, P.; Travlos, A.; Papastaikoudis, C. (Inst. of Mater. Sci., Nat. Res. Centre, Demokritos, Athens, Greece); Hardtke, C.

SO Vacuum (Aug. 1992) vol.43, no.8, p.807-9. 6 refs.

Price: CCCC 0042-207X/92/\$5.00+.00

CODEN: VACUAV ISSN: 0042-207X

DT Journal  
TC Experimental  
CY United Kingdom  
LA English

L4 ANSWER 113 OF 155 INSPEC (C) 2005 IEE on STN



AN 1992:4151034 INSPEC DN A9212-6170W-006

TI Shallow depth profiles of arsenic and boron in CoSi<sub>2</sub> measured by secondary ion mass spectrometry.

AU Mohadjeri, B.; Svensson, B.G. (R. Inst. of Technol., Solid State Electron., Stockholm, Sweden)

SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (Feb. 1992) vol.B64, no.1-4, p.654-8. 12 refs.

Price: CCCC 0168-583X/92/\$05.00

CODEN: NIMBEU ISSN: 0168-583X

Conference: Ion Beam Analysis: Tenth International Conference. Eindhoven, Netherlands, 1-5 July 1991

Sponsor(s): Eindhoven Univ. Technol.; Canberra Ind. Belgium; IBA-9

DT Conference Article; Journal  
TC Experimental  
CY Netherlands  
LA English

L4 ANSWER 114 OF 155 INSPEC (C) 2005 IEE on STN



AN 1992:4085887 INSPEC DN A9206-7360D-001

TI Quantum size effects and grain-boundary scattering in polycrystalline cobalt disilicide films.

AU van der Kraan, R.G.P.; Jongste, J.F.; Jaeger, H.M.; Janssen, G.C.A.M.; Radelaar, S. (Inst. for Microelectronics & Submicron Technol., Delft Univ. of Technol., Netherlands)

SO Physical Review B (Condensed Matter) (15 Dec. 1991) vol.44, no.23, p.13140-3. 17 refs.

CODEN: PRBMDO ISSN: 0163-1829

DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 115 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 1992:4073992 INSPEC DN A9205-6822-004  
 TI Grain boundary composition of pure and boron-doped **cobalt disilicide**.  
 AU Malchere, A.; Gas, P. (Lab. de Metall., Fac. des Sci. et Tech. de St. Jerome, CNRS, Marseille, France); Haut, C.; Larere, A.; Nguyen, T.T.; Poize, S.  
 SO Applied Surface Science (1991) vol.53, p.132-7. 25 refs.  
 Price: CCCC 0169-4332/91/\$03.50  
 CODEN: ASUSEE ISSN: 0169-4332  
 Conference: 1991 European Workshop on Refractory Metals and Silicides. Saltsjobaden, Sweden, 24-27 March 1991  
 Sponsor(s): Royal Inst. Technol. KTH; Swedish Board for Technol. Dev.,STU; Nordiska Balzers; et al  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 116 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 1992:4069920 INSPEC DN A9204-6630F-001  
 TI Cobalt lattice diffusion in bulk **cobalt disilicide**.  
 AU Barge, T.; Poize, S.; Bernardini, J.; Gas, P. (Lab. de Metall., Fac. des Sci. et Tech. de St. Jerome, CNRS, Marseille, France)  
 SO Applied Surface Science (1991) vol.53, p.180-5. 26 refs.  
 Price: CCCC 0169-4332/91/\$03.50  
 CODEN: ASUSEE ISSN: 0169-4332  
 Conference: 1991 European Workshop on Refractory Metals and Silicides. Saltsjobaden, Sweden, 24-27 March 1991  
 Sponsor(s): Royal Inst. Technol. KTH; Swedish Board for Technol. Dev.,STU; Nordiska Balzers; et al  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 117 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 1992:4026840 INSPEC DN A9201-8115N-002  
 TI **Cobalt disilicide** formed by rapid thermal annealing and through-metal arsenic implantation.  
 AU Burte, E.P.; Min Ye (Fraunhofer-Arbeitsgruppe fur Integrierte Schaltungen, Erlangen, Germany)  
 SO Journal of Materials Research (Sept. 1991) vol.6, no.9, p.1892-9. 16 refs.  
 CODEN: JMREEE ISSN: 0884-2914  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 118 OF 155 INSPEC (C) 2005 IEE on STN

Full  
Text

AN 1991:3964556 INSPEC DN A91116690  
 TI **Cobalt disilicide** growth and interface structure analyses.  
 AU D'Anterrosches Meneau, C.; Perret, P. (CNET, CNS, Meylan, France)

SO Philosophical Magazine A (Physics of Condensed Matter, Defects and Mechanical Properties) (June 1991) vol.63, no.6, p.1221-39. 32 refs.  
 Price: CCCC 0141-8610/91/\$3.00  
 CODEN: PMAADG ISSN: 0141-8610  
 DT Journal  
 TC Experimental  
 CY United Kingdom  
 LA English

L4 ANSWER 119 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1991:3930791 INSPEC DN A91097835; B91049812  
 TI Cobalt silicide formation caused by arsenic ion beam mixing and rapid thermal annealing.  
 AU Min Ye; Burte, E.; Pei-Hsin Tsien; Ryssel, H. (Fraunhofer-Arbeitsgruppe fur Integrierte Schaltungen, Erlangen, Germany)  
 SO Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms) (April 1991) vol.B55, no.1-4, p.773-7. 11 refs.  
 Price: CCCC 0168-583X/91/\$03.50  
 CODEN: NIMBEU ISSN: 0168-583X  
 Conference: Eighth International Conference on Ion Implantation Technology (IIT-90). Guildford, UK, 30 July-3 Aug 1990  
 Sponsor(s): IOP; Univ. Surrey  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 120 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1991:3901505 INSPEC DN A91080782  
 TI The structure of **cobalt disilicide** films formed on porous silicon in a solid-state reaction.  
 AU Borisenko, V.E.; Bondarenko, V.P.; Raiko, V.A. (Minsk Radio Eng. Inst., Byelorussian SSR, USSR)  
 SO Physics, Chemistry and Mechanics of Surfaces (1991) vol.6, no.4, p.935-45. 14 refs.  
 CODEN: PCMSER ISSN: 0734-1520  
 Translation of: Poverkhnost'. Fizika, Khimiya, Mekhanika. 14 refs.  
 CODEN: PFKMDJ ISSN: 0207-3528  
 DT Journal; Translation Abstracted  
 TC Experimental  
 CY USSR; United Kingdom  
 LA English

L4 ANSWER 121 OF 155 INSPEC (C) 2005 IEE on STN

Full Text Available

AN 1991:3853137 INSPEC DN A91048300  
 TI Lattice diffusion of boron in bulk **cobalt disilicide**.  
 AU Zaring, C.; Gas, P.; Svensson, B.G.; Ostling, M.; Whitlow, H.J. (Solid State Electron., R. Inst. of Technol., Stockholm, Sweden)  
 SO Thin Solid Films (1 Dec. 1990) vol.193-194, no.1-2, p.244-7. 8 refs.  
 Price: CCCC 0040-6090/90/\$3.50  
 CODEN: THSFAP ISSN: 0040-6090  
 Conference: 17th International Conference on Metallurgical Coatings and 8th International Thin Film Conference. San Diego, CA, USA, 2-6 April 1990

DT Conference Article; Journal  
 TC Theoretical; Experimental  
 CY Switzerland  
 LA English

L4 ANSWER 122 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1991:3848680 INSPEC DN A91048375  
 TI Determination of the elastic constants of a **cobalt disilicide** intermetallic compound.  
 AU Guenin, G. (Group d'Etudes de Metall. Phys. et Phys. des Materiaux, INSA, Villeurbanne, France); Ignat, M.; Thomas, O.  
 SO Journal of Applied Physics (15 Dec. 1990) vol.68, no.12, p.6515-16. 10 refs.  
 Price: CCCC 0021-8979/90/246515-02\$03.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 123 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1991:3841418 INSPEC DN A91042760  
 TI Growth of cobalt and **cobalt disilicide** on Si(100).  
 AU Gallego, J.M.; Miranda, R. (Dept. de Fisica de la Mater. Condensada, Univ. Autonoma de Madrid, Spain); Molodtsov, S.; Laubschat, C.; Kaindl, G.  
 SO Surface Science (Dec. 1990) vol.239, no.3, p.203-12. 36 refs.  
 Price: CCCC 0039-6028/90/\$03.50  
 CODEN: SUSCAS ISSN: 0039-6028  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 124 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1991:3789898 INSPEC DN A91010500; B91001729  
 TI The outdiffusion of boron and arsenic from pre-formed ion-beam-mixed **cobalt disilicide** layers using rapid thermal processing.  
 AU Moynagh, P.B.; Brown, A.A.; Rosser, P.J. (STC Technol. Ltd., Harlow, UK)  
 SO Rapid Thermal Annealing/Chemical Vapor Deposition and Integrated Processing Symposium  
 Editor(s): Hodul, D.; Gelpey, J.C.; Green, M.L.; Seidel, T.E.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1989. p.261-6 of xi+494 pp. 5 refs.  
 Conference: San Diego, CA, USA, 25-28 April 1989  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 125 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1990:3720673 INSPEC DN A90132924  
 TI Quantum transport in ultrathin CoSi<sub>2</sub> epitaxial films.  
 AU DiTusa, J.F.; Parpia, J.M. (Lab. of Atomic & Solid State Phys., Cornell



Univ., Ithaca, NY, USA); Phillips, J.M.

SO Applied Physics Letters (30 July 1990) vol.57, no.5, p.452-4. 27 refs.  
Price: CCCC 0003-6951/90/310452-03\$02.00  
CODEN: APPLAB ISSN: 0003-6951  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 126 OF 155 INSPEC (C) 2005 IEE on STN



AN 1990:3696196 INSPEC DN B90055272  
TI The outdiffusion of boron and arsenic from preformed **cobalt disilicide** layers.  
AU Moynagh, P.B.; Chew, C.P.; Affolter, K.B.; Rosser, P.J. (STC Technol. Ltd., Harlow, UK)  
SO ESSDERC '89. 19th European Solid State Devices Research Conference  
Editor(s): Heuberger, A.; Ryssel, H.; Lange, P.  
Berlin, West Germany: Springer-Verlag, 1989. p.248-52 of xxv+963 pp. 5 refs.  
Conference: Berlin, West Germany, 11-14 Sept 1989  
ISBN: 3-540-51000-1  
DT Conference Article  
TC New Development; Practical; Experimental  
CY Germany, Federal Republic of  
LA English

L4 ANSWER 127 OF 155 INSPEC (C) 2005 IEE on STN



AN 1990:3630180 INSPEC DN A90074455  
TI Arsenic redistribution during cobalt silicide formation.  
AU Pai, C.S.; Baiocchi, F.A.; Williams, D.S. (AT&T Bell Lab., Murray Hill, NJ, USA)  
SO Journal of Applied Physics (1 Feb. 1990) vol.67, no.3, p.1340-6. 20 refs.  
Price: CCCC 0021-8979/90/031340-07\$03.00  
CODEN: JAPIAU ISSN: 0021-8979  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 128 OF 155 INSPEC (C) 2005 IEE on STN



AN 1990:3516486 INSPEC DN B90001378  
TI Resistivity of ion beam synthesised CoSi<sub>2</sub>.  
AU Sealy, B.J.; Tan, B.L.; Gwilliam, R.M.; Reeson, K.J.; Jeynes, C. (Dept. of Electron. & Electr. Eng., Surry Univ., Guildford, UK)  
SO Electronics Letters (26 Oct. 1989) vol.25, no.22, p.1532-3. 15 refs.  
Price: CCCC 0013-5194/89/\$3.00+0.00  
CODEN: ELLEAK ISSN: 0013-5194  
DT Journal  
TC New Development; Practical; Experimental  
CY United Kingdom  
LA English

L4 ANSWER 129 OF 155 INSPEC (C) 2005 IEE on STN



AN 1990:3512394 INSPEC DN A90002787  
 TI Effect of stress on the superconducting properties of CoSi<sub>2</sub> thin films.  
 AU Briggs, A. (Centre de Recherches sur les Tres Basses Temp., CNRS, Grenoble, France); Chroboczek, J.; D'Avitaya, F.A.; Badoz, P.A.  
 SO Thin Solid Films (July 1989) vol.174, p.285-8. 10 refs.  
 Price: CCCC 0040-6090/89/\$3.50  
 CODEN: THSFAP ISSN: 0040-6090  
 Conference: 2nd International Symposium on Trends and New Applications in Thin Films (TATF 89). Regensburg, West Germany, 27 Feb-3 March 1989  
 DT Conference Article; Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L4 ANSWER 130 OF 155 INSPEC (C) 2005 IEE on STN



AN 1989:3500467 INSPEC DN A89142048; B89075612  
 TI Formation of CoSi<sub>2</sub> on amorphous silicon by RTA.  
 AU Drozdy, G.; Ronkainen, H.; Suni, I. (Semicond. Lab., Tech. Res. Center of Finland, Espoo, Finland)  
 SO Applied Surface Science (Sept. 1989) vol.38, no.1-4, p.72-9. 9 refs.  
 Price: CCCC 0169-4332/89/\$03.50  
 CODEN: ASUSEE ISSN: 0169-4332  
 Conference: European Workshop on Refractory Metals and Silicides. Houthalen, Belgium, 20-22 March 1989  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 131 OF 155 INSPEC (C) 2005 IEE on STN



AN 1989:3496331 INSPEC DN A89135469  
 TI Nucleation and growth of ultrathin epitaxial metal silicides on silicon.  
 AU Batstone, J.L.; Tung, R.T.; Phillips, J.M.; Gibson, J.M. (AT&T Bell Labs., Murray Hill, NJ, USA)  
 SO Epitaxy of Semiconductor Layered Structures: Symposium  
 Editor(s): Tung, R.T.; Dawson, L.R.; Gunshor, R.L.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1988. p.253-8 of xiii+609 pp. 19 refs. Availability: Clarke Associates - Europe, West Molesey, UK  
 Conference: Boston, MA, USA, 30 Nov-4 Dec 1987  
 ISBN: 0-931837-70-7  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 132 OF 155 INSPEC (C) 2005 IEE on STN



AN 1989:3480094 INSPEC DN B89069128  
 TI An improved self aligned silicide process for VLSI.  
 AU Singh, A.; Khokle, W.S. (Semicond. Devices Area, CEERI, Raj, India)  
 SO Microelectronics Journal (July-Aug. 1989) vol.20, no.4, p.11-17. 5 refs.  
 CODEN: MICEB9 ISSN: 0026-2692  
 DT Journal

TC Practical; Experimental  
CY United Kingdom  
LA English

L4 ANSWER 133 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3397248 INSPEC DN A89077031  
TI Two-step annealing for **cobalt disilicide** formation with lowest sheet resistance.  
AU Singh, A. (CEERI, Pilani, India)  
SO Physica Status Solidi A (16 Feb. 1989) vol.111, no.2, p.K191-3. 7 refs.  
CODEN: PSSABA ISSN: 0031-8965  
DT Journal  
TC Experimental  
CY German Democratic Republic  
LA English

L4 ANSWER 134 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3292181 INSPEC DN A89018812  
TI The diffusion of elements implanted in films of **cobalt disilicide**.  
AU Thomas, O.; Gas, P.; Charai, A.; LeGoues, F.K.; Michel, A.; Scilla, G.; d'Heurle, F.M. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)  
SO Journal of Applied Physics (15 Sept. 1988) vol.64, no.6, p.2973-80. 42 refs.  
Price: CCCC 0021-8979/88/182973-08\$02.40  
CODEN: JAPIAU ISSN: 0021-8979  
DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 135 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3290072 INSPEC DN B89009117  
TI Organometallic chemical vapor deposition of cobalt and formation of **cobalt disilicide**.  
AU Gross, M.E.; Schnoes Kranz, K.; Brasen, D.; Luftman, H. (AT&T Bell Labs., Murray Hill, NJ, USA)  
SO Journal of Vacuum Science & Technology B (Microelectronics Processing and Phenomena) (Sept.-Oct. 1988) vol.6, no.5, p.1548-52. 16 refs.  
Price: CCCC 0734-211X/88/051548-05\$01.00  
CODEN: JVTBD9 ISSN: 0734-211X  
DT Journal  
TC Application; New Development; Practical; Experimental  
CY United States  
LA English

L4 ANSWER 136 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3279033 INSPEC DN A89009140; B89000696  
TI Chemical vapor deposition of cobalt and formation of **cobalt disilicide**.  
AU Gross, M.E.; Schnoes, K.J. (AT&T Bell Labs., Murray Hill, NJ, USA)  
SO Proceedings of the Tenth International Conference on Chemical Vapor Deposition 1987

Editor(s): Cullen, G.W.; Blocher, J.M., Jr.

Pennington, NJ, USA: Electrochem. Soc, 1987. p.759-65 of xvi+1269 pp. 14 refs.

Conference: Honolulu, HI, USA, Oct 1987

Sponsor(s): Electrochem. Soc. Japan; Japan Soc. Appl. Phys

DT Conference Article

TC Experimental

CY United States

LA English

L4 ANSWER 137 OF 155 INSPEC (C) 2005 IEE on STN



AN 1988:3259408 INSPEC DN B88071466

TI Formation and oxidation of implanted cobalt silicides on polycrystalline-silicon.

AU Kozicki, M.N. (Coll. of Eng. & Appl. Sci., Arizona State Univ., Tempe, AZ, USA)

SO 1988 Proceedings. Fifth International IEEE VLSI Multilevel Interconnection Conference (Cat. No.88CH2624-5)

New York, NY, USA: IEEE, 1988. p.198-204 of 497 pp. 2 refs.

Conference: Santa Clara, CA, USA, 13-14 June 1988

Sponsor(s): IEEE

Price: CCCC CH2624-5/88/0000-0198\$01.00

DT Conference Article

TC Practical; Experimental

CY United States

LA English

L4 ANSWER 138 OF 155 INSPEC (C) 2005 IEE on STN



AN 1988:3221686 INSPEC DN A88123847

TI Diffusion of boron, phosphorus, and arsenic implanted in thin films of **cobalt disilicide**.

AU Thomas, O.; Gas, P.; d'Heurle, F.M.; LeGoues, F.K.; Michel, A.; Scilla, G. (IBM Thomas J. Watson Res. Center, Yorktown Heights, NY, USA)

SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1988) vol.6, no.3, pt.2, p.1736-9. 26 refs.

Price: CCCC 0734-2101/88/031736-04\$01.00

CODEN: JVTAD6 ISSN: 0734-2101

Conference: 34th National Symposium of the American Vacuum Society. Anaheim, CA, USA, 2-6 Nov 1987

DT Conference Article; Journal

TC Experimental

CY United States

LA English

L4 ANSWER 139 OF 155 INSPEC (C) 2005 IEE on STN



AN 1988:3216715 INSPEC DN A88117560

TI Electronic structure of **cobalt disilicide**.

AU Newcombe, G.C.F.; Lonzarich, G.G. (Cavendish Lab., Cambridge Univ., UK)

SO Physical Review B (Condensed Matter) (15 June 1988) vol.37, no.18, p.10619-22. 10 refs.

CODEN: PRBMDO ISSN: 0163-1829

DT Journal

TC Experimental

CY United States

LA English

L4 ANSWER 140 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3132953 INSPEC DN B88033165  
 TI Technology for submicrometer Si/CoSi<sub>2</sub> epitaxial permeable-base transistor.  
 AU Glastre, G.; Vincent, G.; Vareille, A.; Puissant, C.; Rosencher, E. (CNET, Meylan, France)  
 SO IEEE Transactions on Electron Devices (Nov. 1987) vol.ED-34, no.11, p.2368. 0 refs.  
 CODEN: IETDAI ISSN: 0018-9383  
 Conference: 45th Annual Device Research Conference (papers in summary form only received). Santa Barbara, CA, USA, 22-24 June 1987  
 Sponsor(s): IEEE  
 DT Conference Article; Journal  
 TC Application; Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 141 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3072104 INSPEC DN B88013176  
 TI Self-aligned **cobalt disilicide** for gate and interconnection and contacts to shallow junctions.  
 AU Murarka, S.P. (Rensselaer Polytech. Inst., Troy, NY, USA); Fraser, D.B.; Sinha, A.K.; Levinstein, H.J.; Lloyd, E.J.; Liu, R.; Williams, D.S.; Hillenius, S.J.  
 SO IEEE Transactions on Electron Devices (Oct. 1987) vol.ED-34, no.10, p.2108-15. 28 refs.  
 Price: CCCC 0018-9383/87/1000-2108\$01.00  
 CODEN: IETDAI ISSN: 0018-9383  
 DT Journal  
 TC Application; New Development; Practical; Experimental  
 CY United States  
 LA English

L4 ANSWER 142 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1988:3070490 INSPEC DN B88013004  
 TI Stability of polycrystalline silicon-on-**cobalt disilicide**-silicon structures.  
 AU Murarka, S.P. (Dept. of Mater. Eng., Rensselaer Polytech. Inst., Troy, NY, USA); Chang, C.C.; Adams, A.C.  
 SO Journal of Vacuum Science & Technology B (Microelectronics Processing and Phenomena) (July-Aug. 1987) vol.5, no.4, p.865-9. 14 refs.  
 Price: CCCC 0734-211X/87/040865-05\$01.00  
 CODEN: JVTBD9 ISSN: 0734-211X  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 143 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1987:2928339 INSPEC DN A87077818; B87045893  
 TI Silicon overgrowth on CoSi<sub>2</sub>/Si(111) epitaxial structures: application to

permeable base transistor.

AU Arnaud d'Avitaya, F.; Chroboczek, J.A.; D'Anterrockes, C.; Glastre, G.; Campidelli, Y.; Rosencher, E. (CNET, Meylan, France)  
 SO Journal of Crystal Growth (Feb. 1987) vol.81, no.1-4, p.463-9. 11 refs.  
 Price: CCCC 0022-0248/87/\$03.50  
 CODEN: JCRGAE ISSN: 0022-0248  
 Conference: Fourth International Conference on Molecular Beam Epitaxy.  
 York, UK, 7-10 Sept 1986  
 Sponsor(s): British Assoc. Crystal Growth  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L4 ANSWER 144 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1986:2745372 INSPEC DN A86112729  
 TI TiC as a diffusion barrier between Al and CoSi<sub>2</sub>.  
 AU Appelbaum, A.; Murarka, S.P. (AT&T Bell Labs., Murray Hill, NJ, USA)  
 SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films)  
 (May-June 1986) vol.4, no.3, pt.1, p.637-40. 16 refs.  
 Price: CCCC 0734-2101/86/030637-04\$01.00  
 CODEN: JVTAD6 ISSN: 0734-2101  
 Conference: Proceedings of the 32nd National Symposium of the American  
 Vacuum Society. Houston, TX, USA, 19-22 Nov 1985  
 DT Conference Article; Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 145 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1986:2665412 INSPEC DN A86064334  
 TI Structural reactions of Si(111) with cobalt and formation of **cobalt disilicide**.  
 AU Wu, S.C.; Wang, Z.Q.; Li, Y.S.; Jona, F. (Coll. of Eng. & Appl. Sci., State Univ. of New York, Stony Brook, NY, USA); Marcus, P.M.  
 SO Physical Review B (Condensed Matter) (15 Feb. 1986) vol.33, no.4, p.2900-2. 13 refs.  
 CODEN: PRBMDO ISSN: 0163-1829  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L4 ANSWER 146 OF 155 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1986:2558436 INSPEC DN A86004817  
 TI Experimental investigations on the oxidation of **cobalt disilicide** (CoSi<sub>2</sub>).  
 AU Kim, S.-J.; Banwell, T.C.; Shima, R.; Nicolet, M.-A. (Electr. Eng., California Inst. of Technol., Pasadena, CA, USA)  
 SO Proceedings of the SPIE - The International Society for Optical Engineering (1985) vol.530, p.152-8. 9 refs.  
 CODEN: PSISDG ISSN: 0277-786X  
 Conference: Advanced Applications of Ion Implantation. Los Angeles, CA, USA, 23-25 Jan 1985  
 DT Conference Article; Journal

TC Experimental  
CY United States  
LA English

L4 ANSWER 147 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2534170 INSPEC DN B85055791  
TI A Si permeable base transistor by metal/semiconductor hetero-epitaxy.  
AU Ishibashi, K.; Furukawa, S. (Tokyo Inst. of Technol., Yokohama, Japan)  
SO International Electron Devices Meeting. Technical Digest (Cat. No. 84CH2099-0)  
New York, NY, USA: IEEE, 1984. p.868-70 of 875 pp. 2 refs.  
Conference: San Francisco, CA, USA, 9-12 Dec 1984  
Sponsor(s): IEEE  
Price: CCCC CH2099-0/84/0000-0868\$01.00

DT Conference Article  
TC New Development; Practical  
CY United States  
LA English

L4 ANSWER 148 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2455212 INSPEC DN A85066563  
TI Study of **cobalt-disilicide** formation from cobalt monosilicide.  
AU Appelbaum, A.; Knoell, R.V.; Murarka, S.P. (AT&T Bell Labs., Murray Hill, NJ, USA)  
SO Journal of Applied Physics (15 March 1985) vol.57, no.6, p.1880-6. 18 refs.  
Price: CCCC 0021-8979/85/061880-07\$02.40  
CODEN: JAPIAU ISSN: 0021-8979

DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 149 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2425224 INSPEC DN A85038646; B85022525  
TI Cosputtered cobalt silicides on silicon, polycrystalline silicon, and silicon dioxide.  
AU Murarka, S.P.; Vaidya, S. (AT&T Bell Labs., Murray Hill, NJ, USA)  
SO Journal of Applied Physics (15 Dec. 1984) vol.56, no.12, p.3404-12. 20 refs.  
Price: CCCC 0021-8979/84/243404-09\$02.40  
CODEN: JAPIAU ISSN: 0021-8979

DT Journal  
TC Practical; Experimental  
CY United States  
LA English

L4 ANSWER 150 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1985:2415980 INSPEC DN A85039373  
TI **Cobalt disilicide**: crystal growth and physical properties.  
AU Ditchek, B.M. (GTE Labs., Waltham, MA, USA)  
SO Journal of Crystal Growth (Nov. 1984) vol.69, no.1, p.207-10. 13 refs.

Price: CCCC 0022-0248/84/\$03.00

CODEN: JCRGAE ISSN: 0022-0248

DT Journal  
TC Experimental  
CY Netherlands  
LA English

L4 ANSWER 151 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1984:2250876 INSPEC DN A84061844

TI **Cobalt disilicide** epitaxial growth on the silicon (111) surface.

AU Pirri, C.; Peruchetti, J.C.; Gewinner, G. (Inst. des Sci. Exactes et Appliquees, Univ. de Haute-Alsace, Mulhouse, France); Derrien, J.

SO Physical Review B (Condensed Matter) (15 March 1984) vol.29, no.6, p.3391-7. 38 refs.

CODEN: PRBMDO ISSN: 0163-1829

DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 152 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1983:1984454 INSPEC DN A83014753; B83007325

TI Thermal oxidation of **cobalt disilicide**.

AU Bartur, M.; Nicolet, M.-A. (California Inst. of Technol., Pasadena, CA, USA)

SO Applied Physics A (Solids and Surfaces) (Oct. 1982) vol.A29, no.2, p.69-70. 9 refs.

Price: CCCC 0721-7250/82/0029/0069/\$01.00

CODEN: APSFDB ISSN: 0721-7250

DT Journal  
TC Experimental  
CY Germany, Federal Republic of  
LA English

L4 ANSWER 153 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1983:1974116 INSPEC DN A83008343

TI Direct determination of atomic structure at the epitaxial **cobalt disilicide** on (111) Si interface by ultrahigh resolution electron microscopy.

AU Gibson, J.M.; Bean, J.C.; Poate, J.M.; Tung, R.T. (Bell Labs., Murray Hill, NJ, USA)

SO Applied Physics Letters (1 Nov. 1982) vol.41, no.9, p.818-20. 7 refs.

Price: CCCC 0003-6951/82/090818-03\$01.00

CODEN: APPLAB ISSN: 0003-6951

DT Journal  
TC Experimental  
CY United States  
LA English

L4 ANSWER 154 OF 155 INSPEC (C) 2005 IEE on STN

Full Text

AN 1970:202621 INSPEC DN A70078791

TI Thermal and electrical conductivity of **cobalt disilicide**.



AU Krentsis, R.P.; Ostrovskii, F.I.; Frolov, A.A.; Gel'd, P.V.  
 SO Izvestiya Vysshikh Uchebnykh Zavedenii, Fizika (1970) no.8, p.157-8  
 CODEN: IVUFAC ISSN: 0021-3411  
 Translation in: Soviet Physics Journal  
 CODEN: SOPJAO ISSN: 0038-5697  
 DT Journal; Original Abstracted  
 CY USSR; United States  
 LA Russian

L4 ANSWER 155 OF 155 INSPEC (C) 2005 IEE on STN



AN 1969:5639 INSPEC DN A69003480  
 TI Solid solutions of disilicides of nickel and cobalt.  
 AU Sidorenko, F.A.; Miroshnikov, L.A.; Gel'd, P.V.  
 SO Izvestiya Vysshikh Uchebnykh Zavedenii, Fizika (1968) no.5, p.70-5  
 CODEN: IVUFAC ISSN: 0021-3411  
 Translation in: Soviet Physics Journal  
 CODEN: SOPJAO ISSN: 0038-5697  
 DT Journal; Original Abstracted  
 CY USSR; United States  
 LA Russian

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